

Faculty of Engineering
School of Photovoltaic and Renewable Energy Engineering



Light- and Elevated Temperature-Induced Degradation (LeTID): **the Past**, **the Present** and **What Lies Ahead**

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Light- and Elevated Temperature Induced Degradation (LeTID)

- LeTID is now a very well known in both academia and industry



MEYER BURGER



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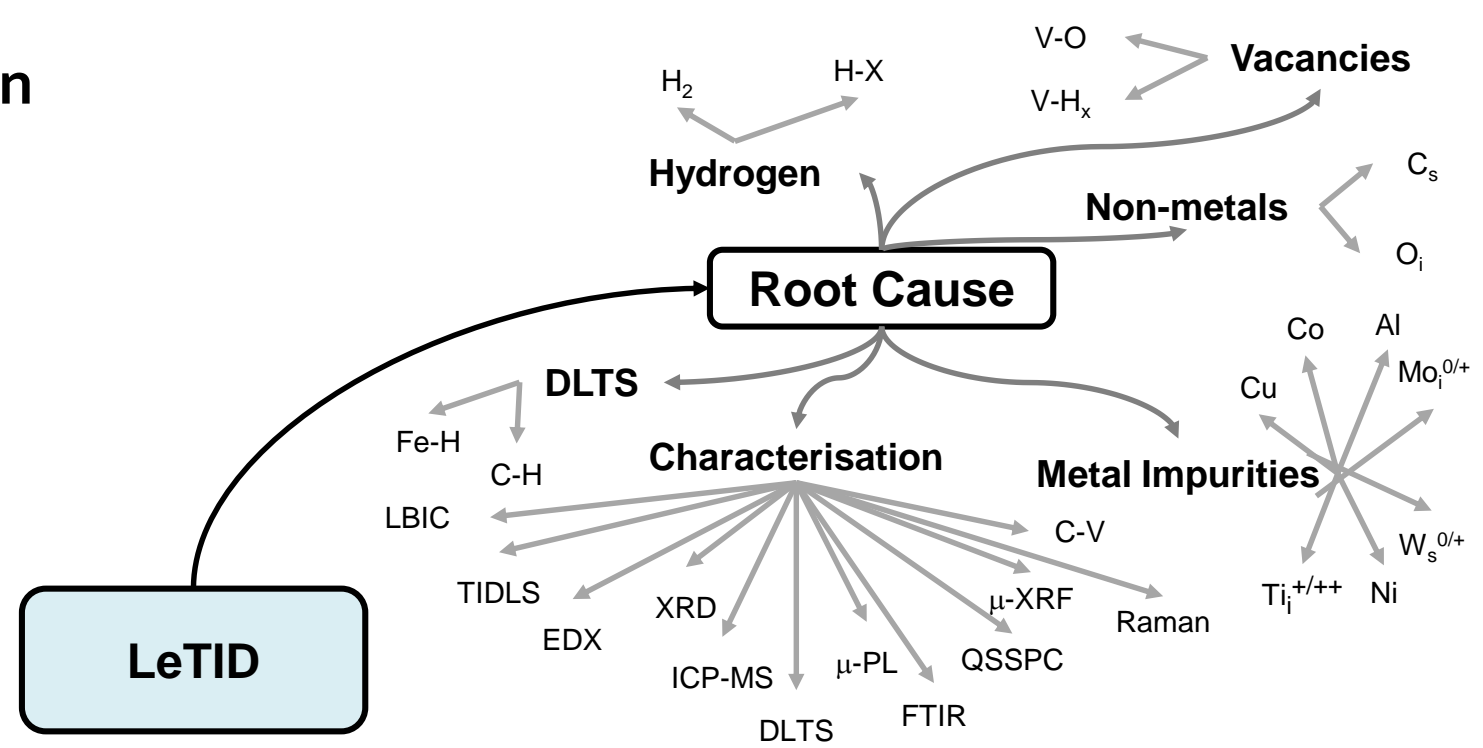


- There have been over 200 conference and journal publications worldwide

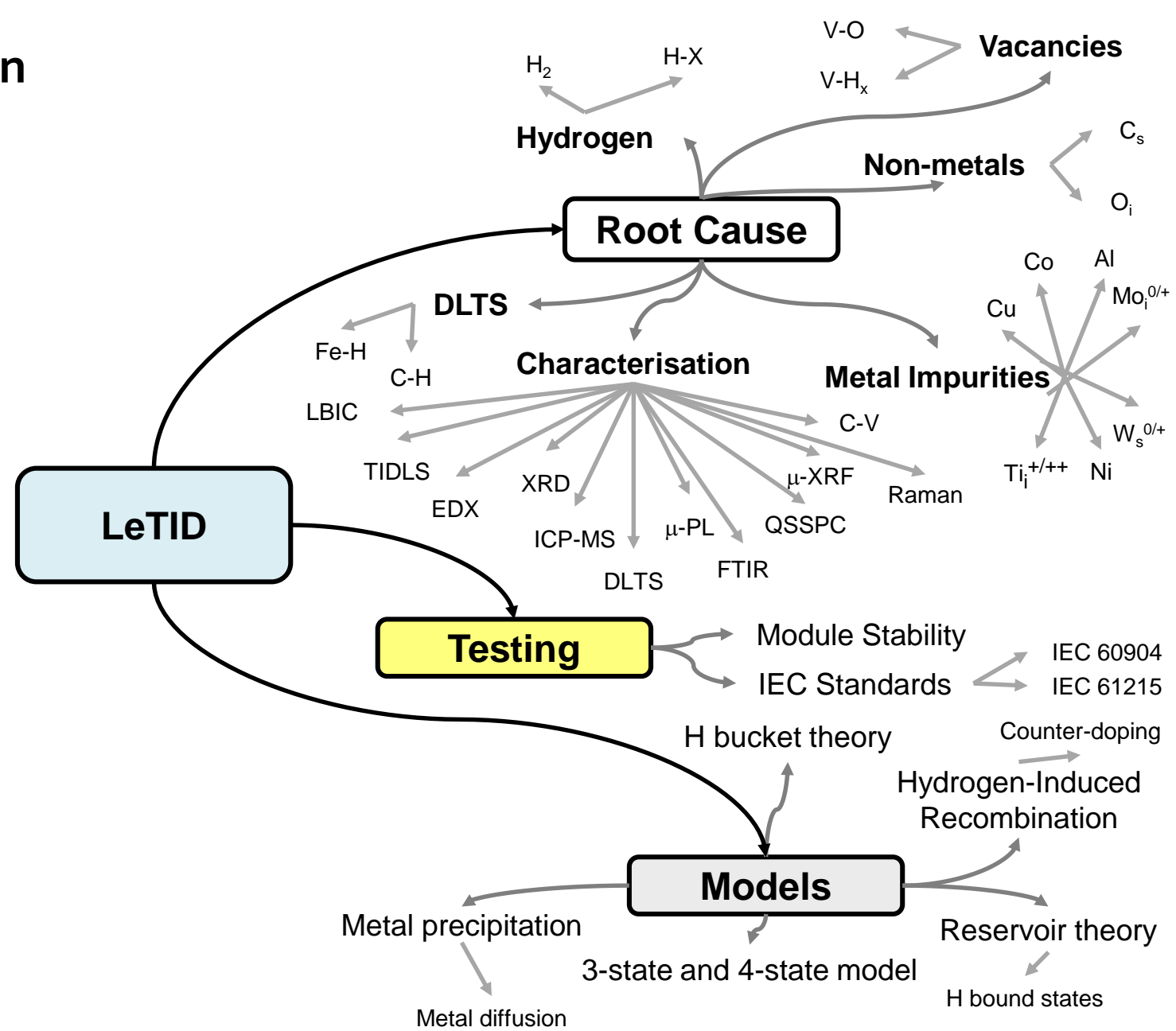
LeTID – Key Areas of Investigation

LeTID

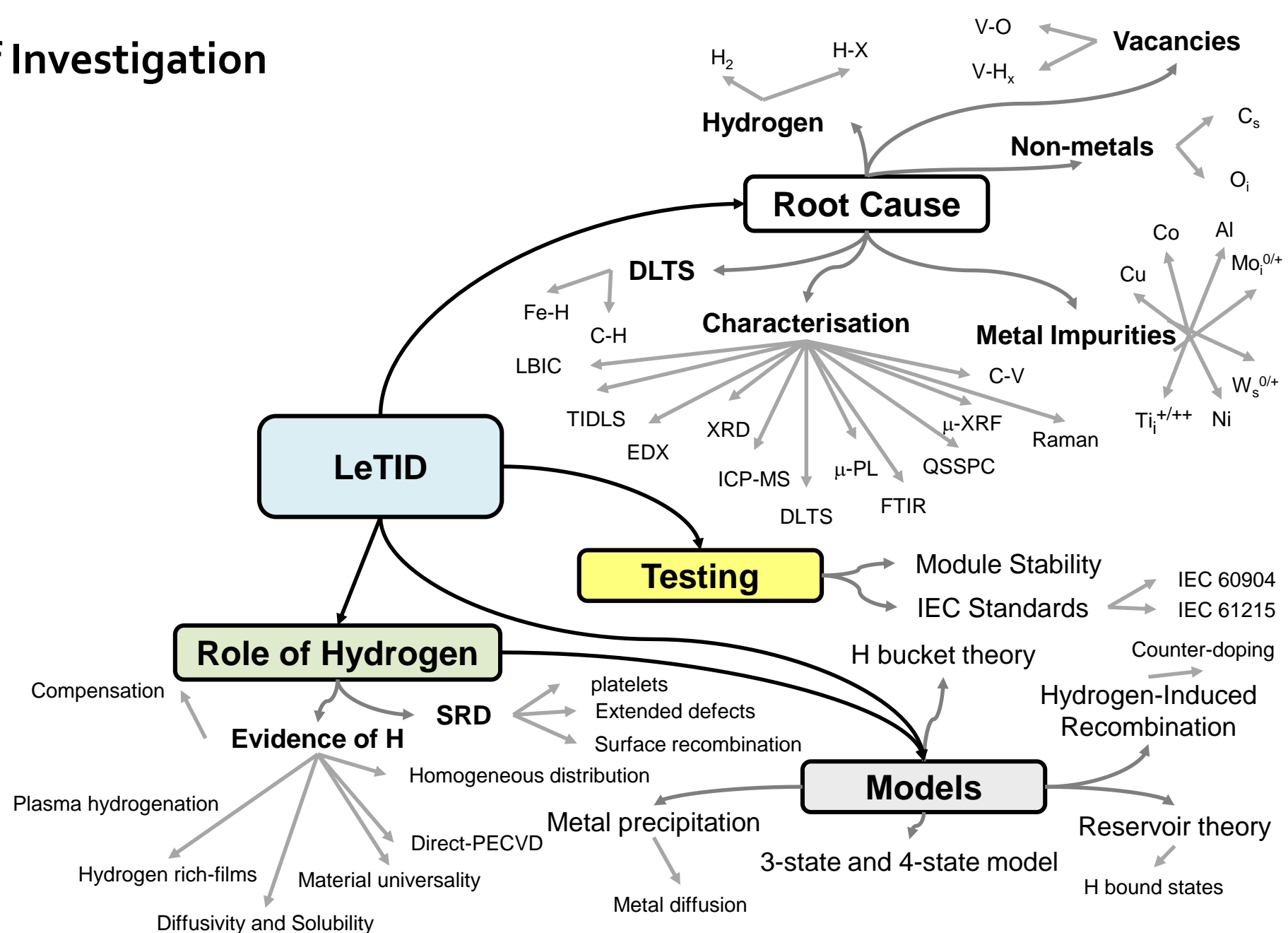
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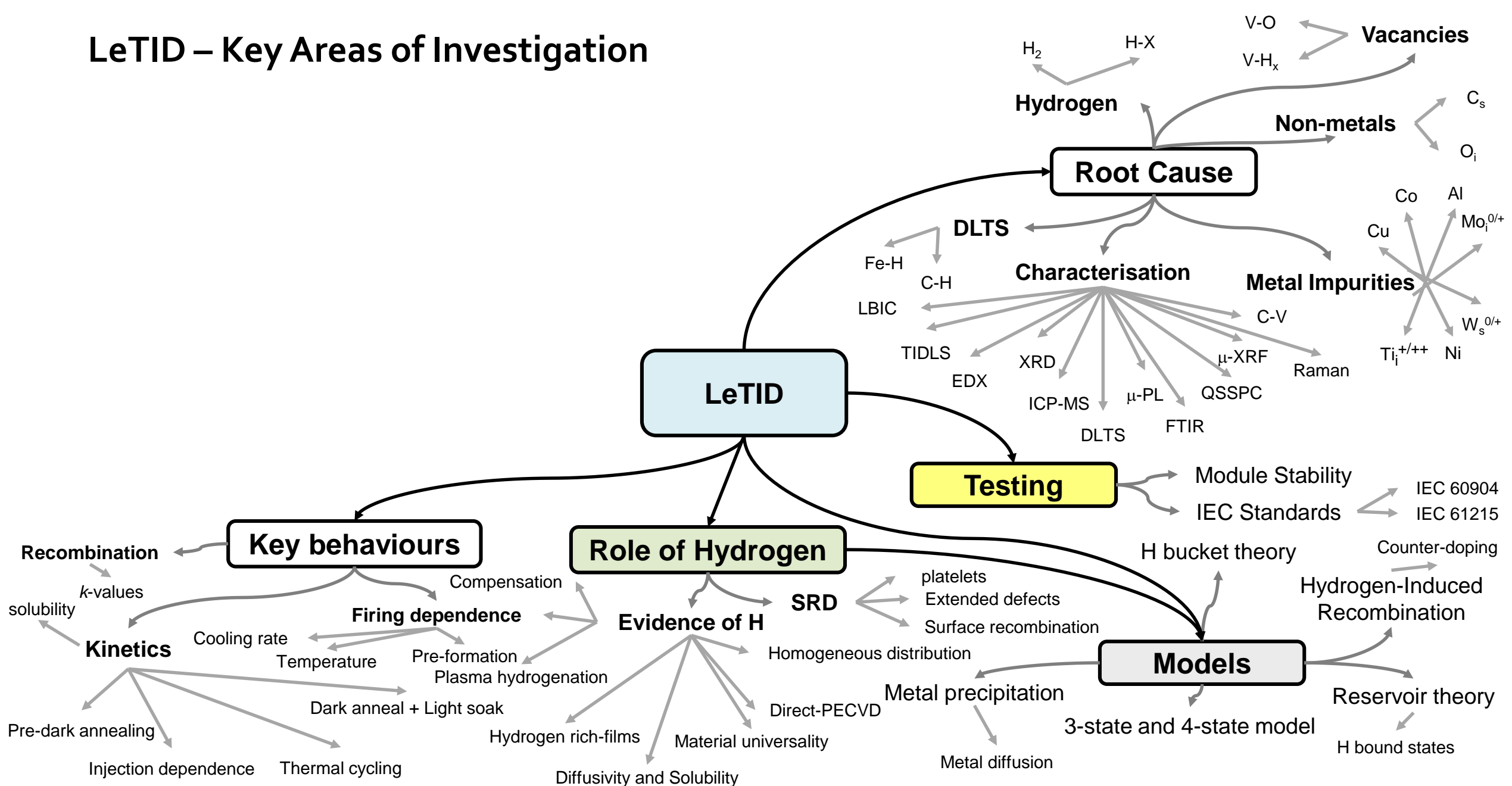
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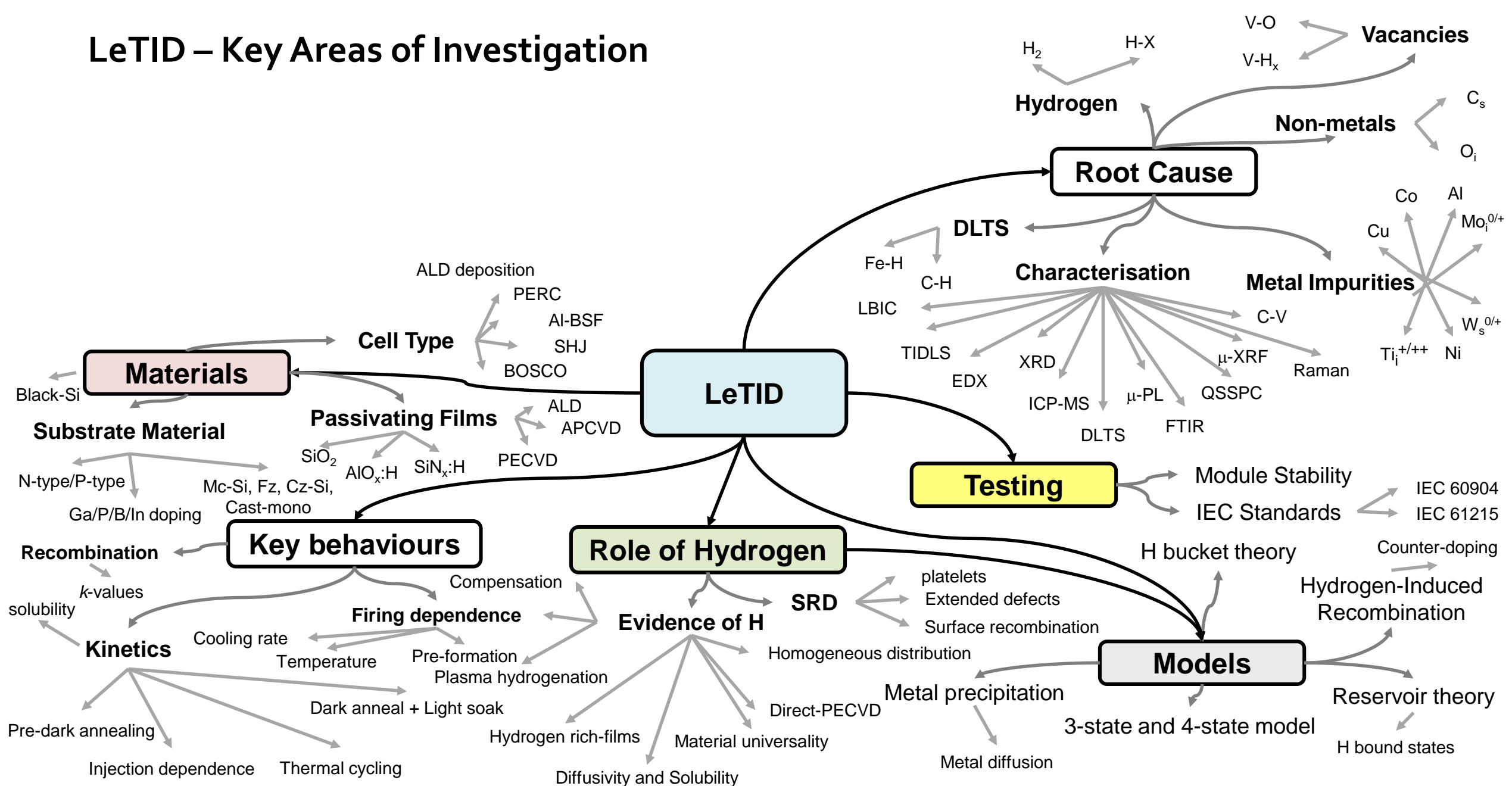
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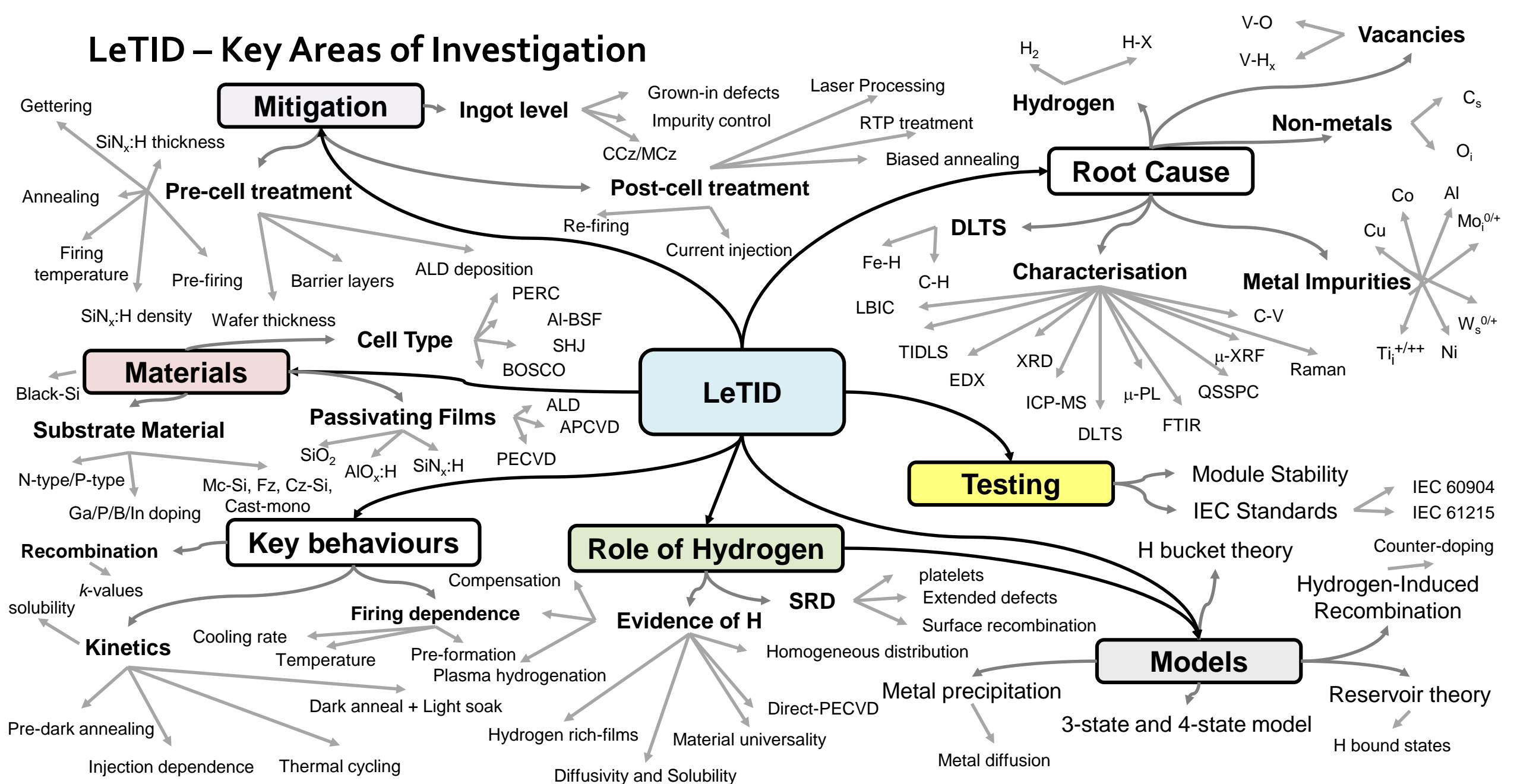
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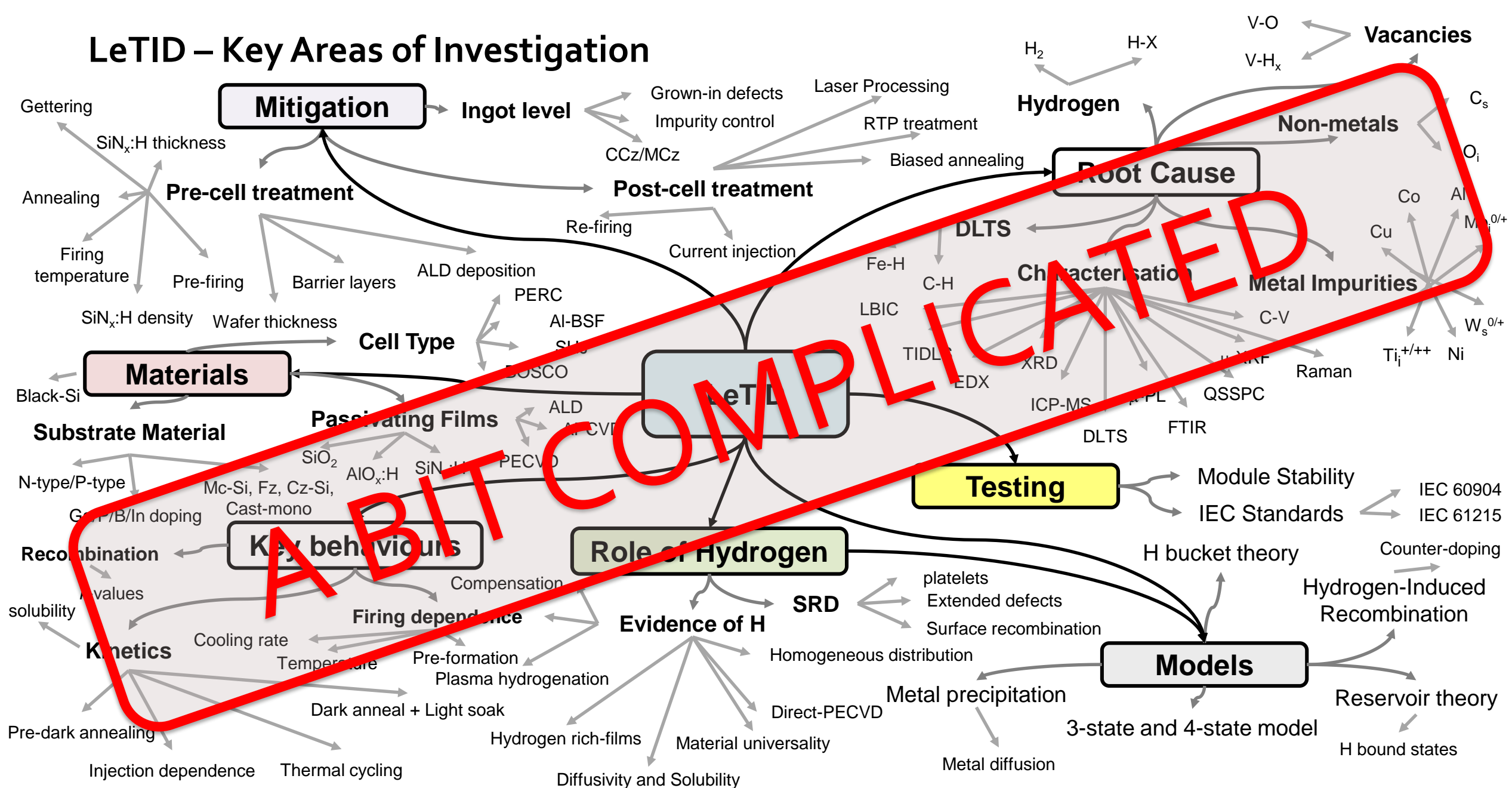
LeTID – Key Areas of Investigation



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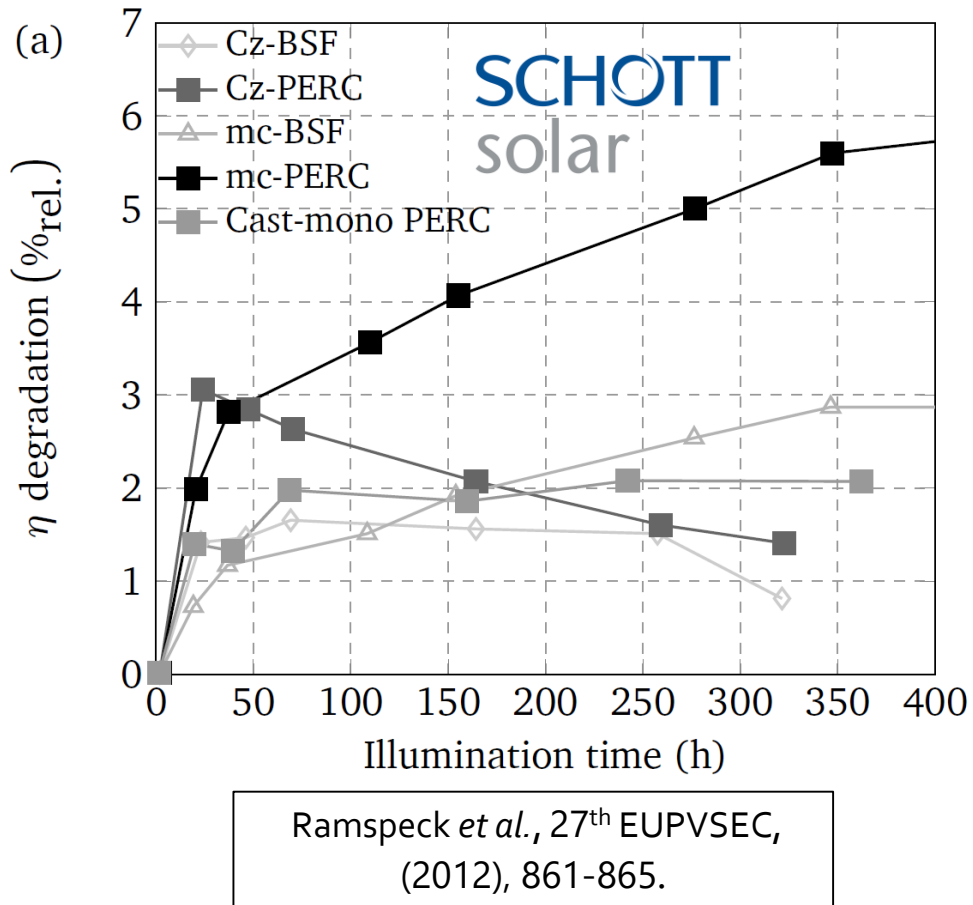
LeTID – Key Areas of Investigation



Presentation Outline

1. A brief history of LeTID
2. Evaluating the Root Cause of LeTID
3. Our proposed LeTID model
4. Mitigation Strategies for LeTID
Is LeTID going to be a problem for the industry?
What happens after LeTID?

The Past – Beginnings of LeTID

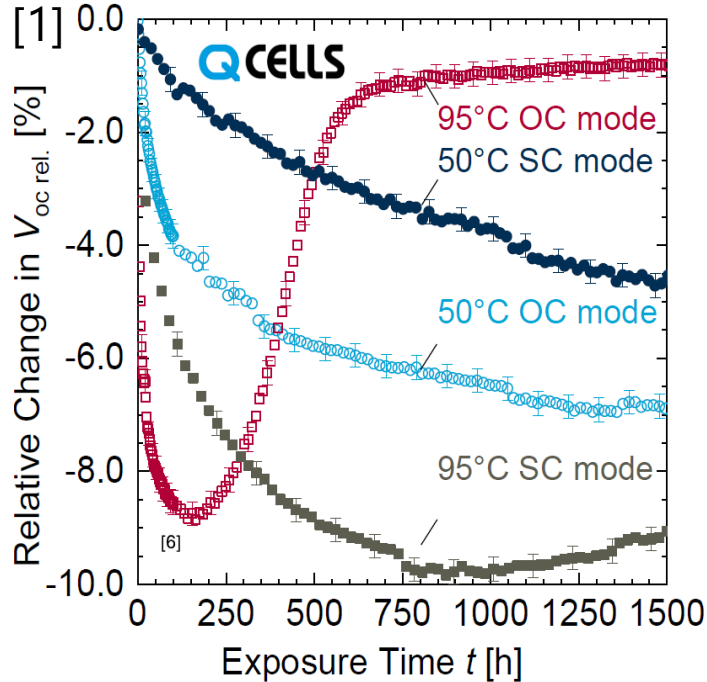


Reference	Type	Rel. Deg	Condition
Sio <i>et al.</i>	Cell	4.3%	65 °C, 1sun
Chan <i>et al.</i>	Cell	12.7%	70 °C, 0.46 kW/m ²
Luka <i>et al.</i>	Cell	10%	75 °C, 1sun
Ramspeck <i>et al.</i>	Cell	6%	75 °C, 0.4 kW/m ²
Petter <i>et al.</i>	Cell	16%	75 °C, 1sun
Deniz <i>et al.</i>	Cell	4.4%	75 °C, J _{SC}
Krauss <i>et al.</i>	Cell	11.2%	80 °C, 0.8 kW/m ²
Fertig <i>et al.</i>	Module	11%	85 °C, MPP, 1 kW/m ²
Kersten <i>et al.</i>	Module	11%	85 °C, MPP
Nakayashiki <i>et al.</i>	Module	7.5%	Outdoor
Kersten <i>et al.</i>	Module	10%	Outdoor

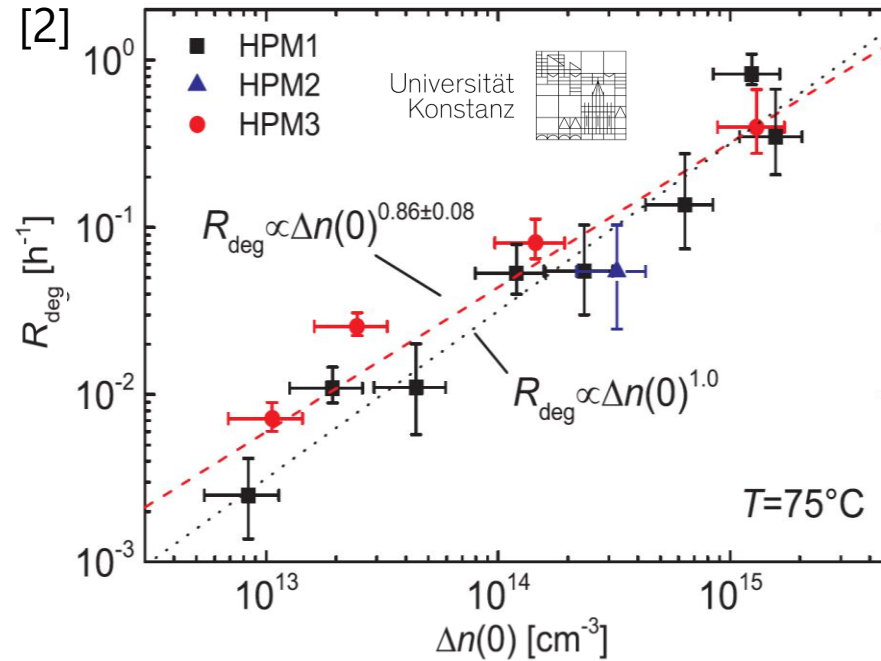
- First identified in 2012 on mc-PERC solar cells by Ramspeck *et al.*
- Average degradation in efficiency of up to 10%_{rel} on **untreated cells** and as much as 16%_{rel} in some studies

The Past – Early Observations

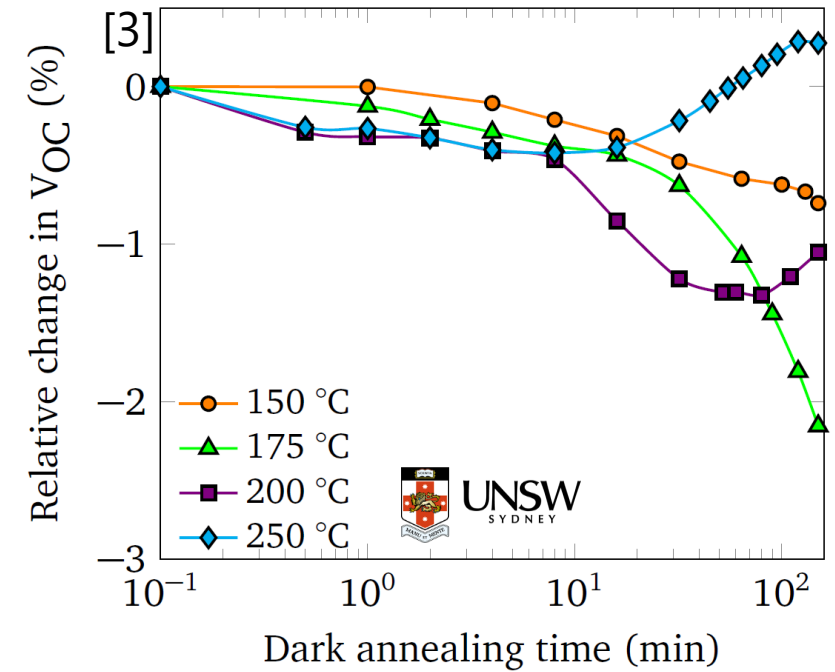
- In 2015, Kersten *et al.* showed that the degradation was accelerated at higher T, thus calling it LeTID



Kersten *et al.*, Sol. Energy Mater. Sol. Cells. 142 (2015) 83–86



Kwapil *et al.*, Sol. Energy Mater. Sol. Cells, 173 (2017), 80–84

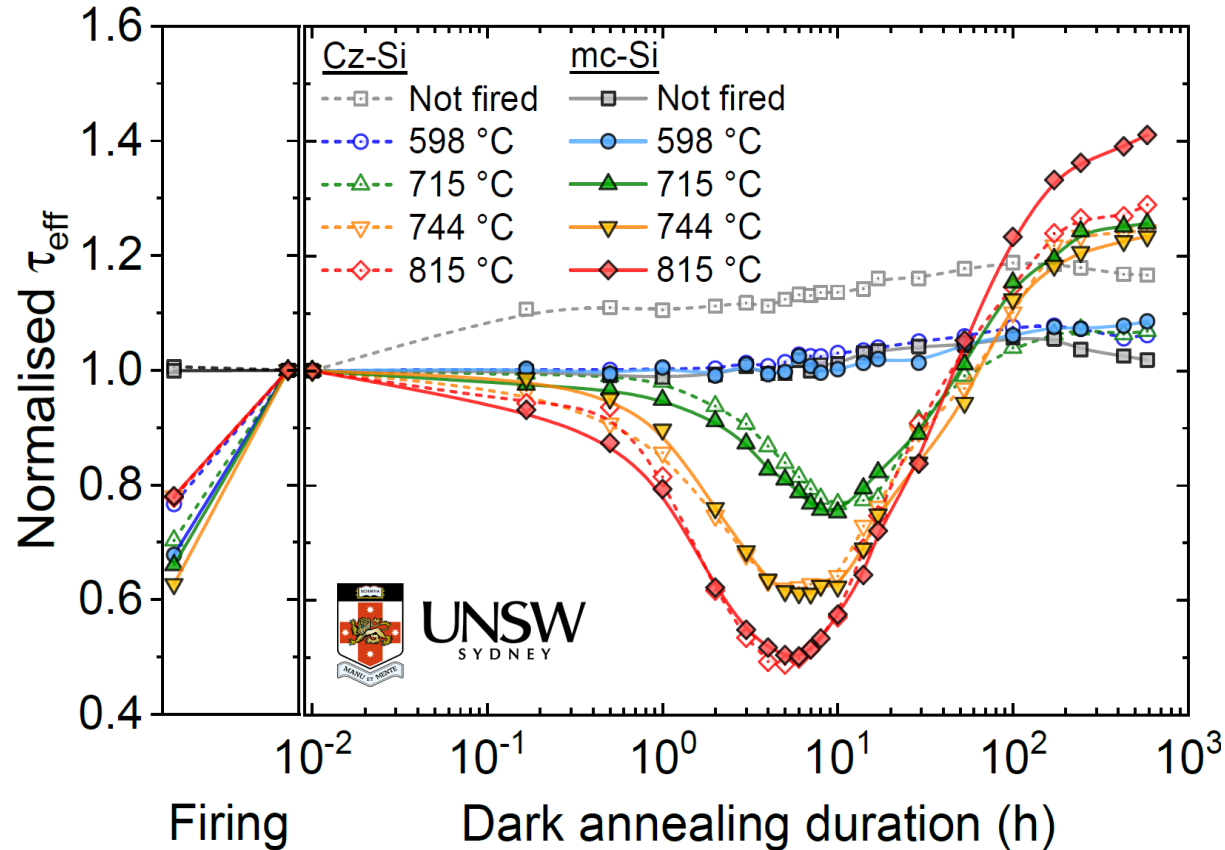


Chan *et al.*, Sol. RRL. 1 (2017) 1600028.

- Later in 2017, Kwapil *et al.* demonstrated a dependence of the degradation reaction on Δn . Adding illumination increases the reaction rate.
- In 2017, Chan *et al.* observed that degradation also occurs during dark annealing

The Past – A Discovery of LeTID in Czochralski

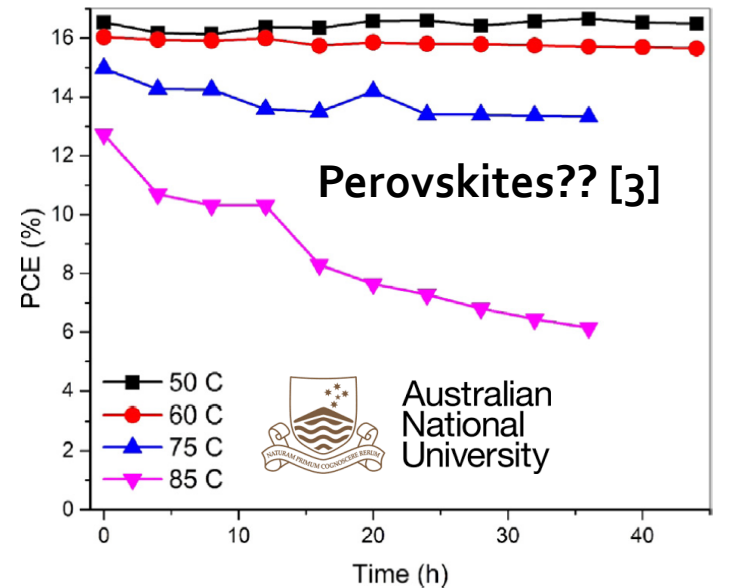
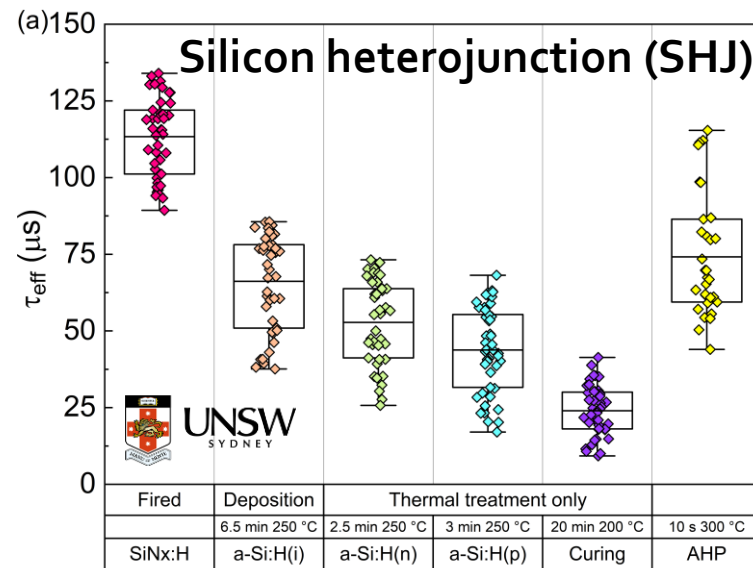
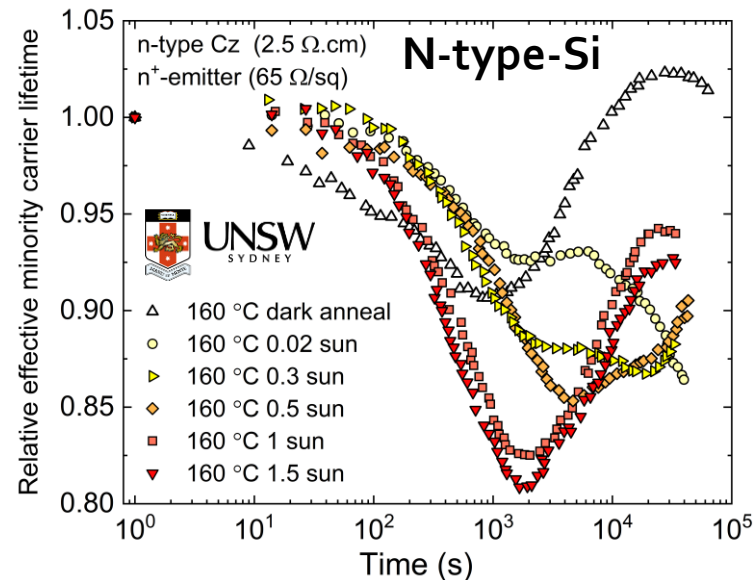
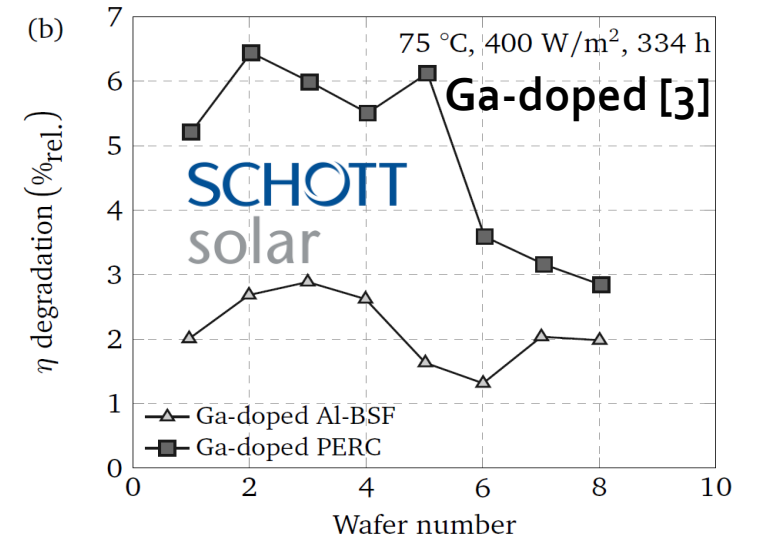
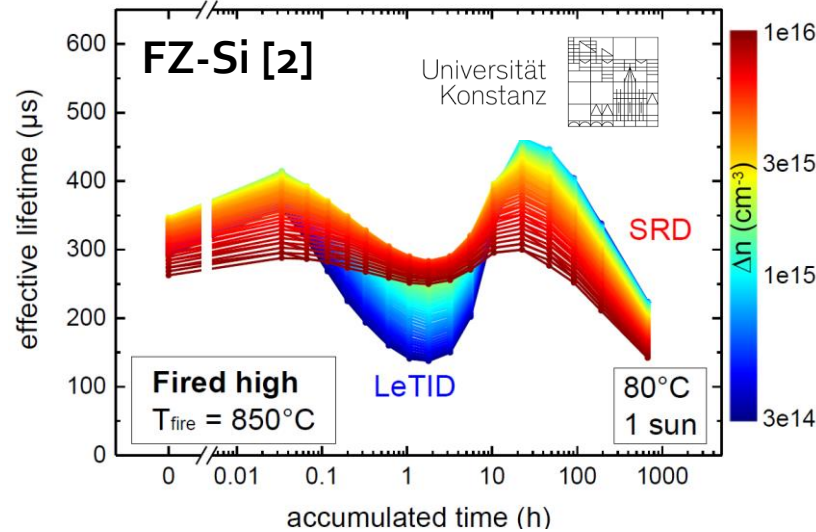
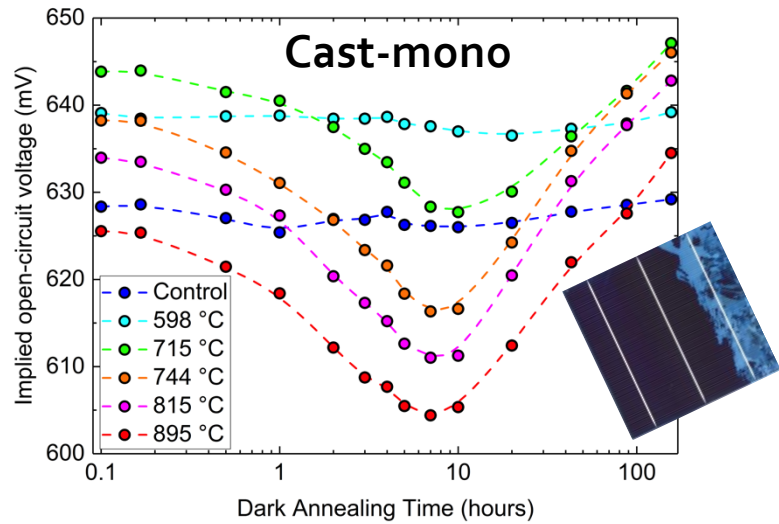
- This provided a method of testing p-type Cz wafers without activating B-O defects



Chen *et al.*, Sol. Energy Mater. Sol. Cells. 172 (2017) 293–300.

- As part of my PhD, we showed that LeTID also manifests itself in Cz materials

The Past – A Universal Defect in Silicon



[1] Sperber *et al.*, AIP Conf. Proc., 2019: p. 140011.

[2] Ramspeck *et al.*, 27th EUPVSEC, (2012), 861-865.

[3] Duong *et al.*, Sol. Energy Mater. Sol. Cells.

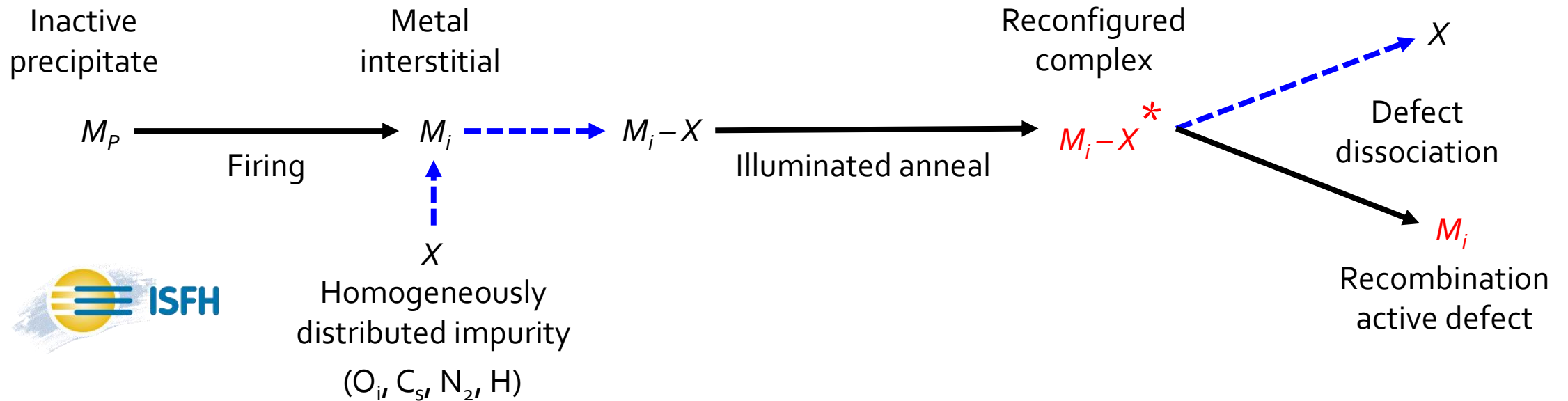
188 (2018) 27–36.

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The Past – Evaluating the Root Cause – Metal Impurities

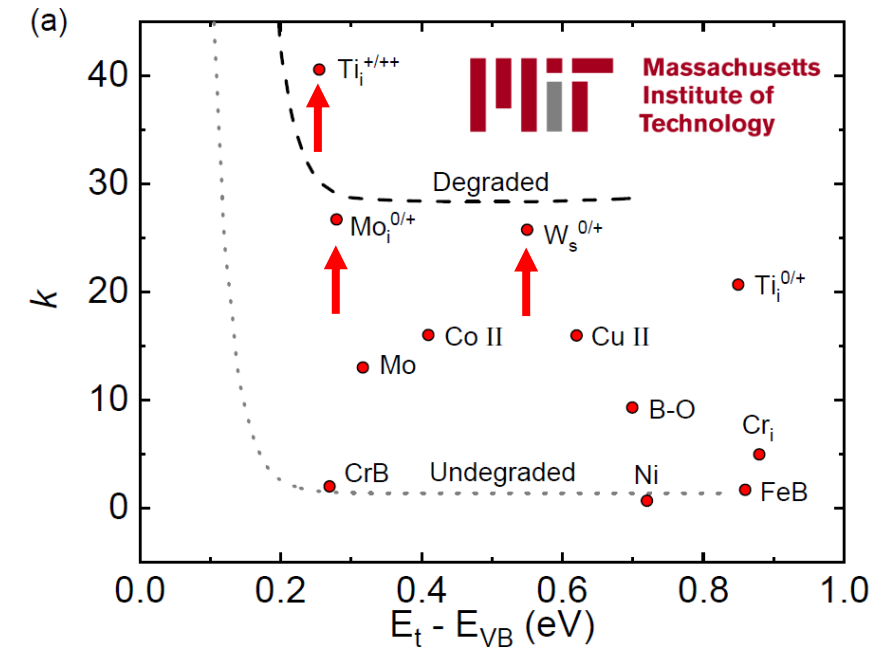
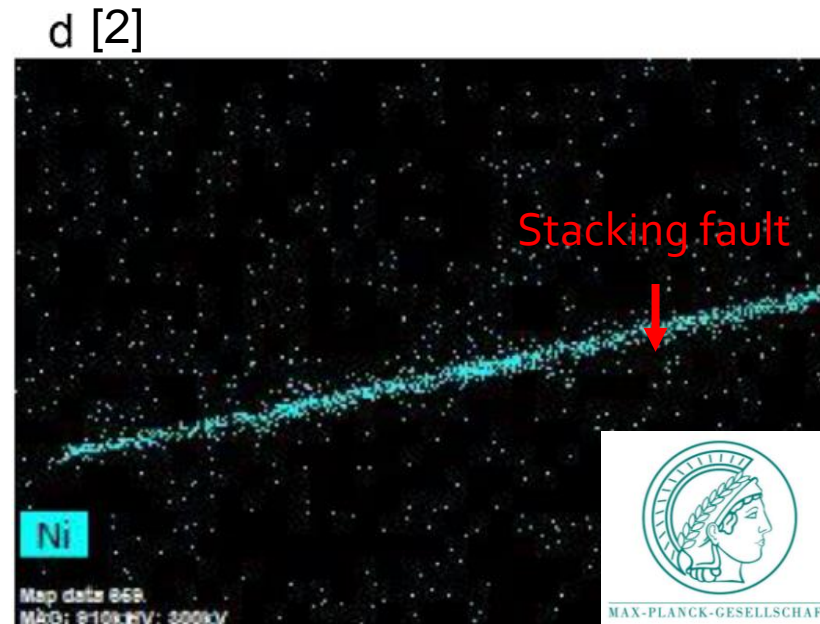
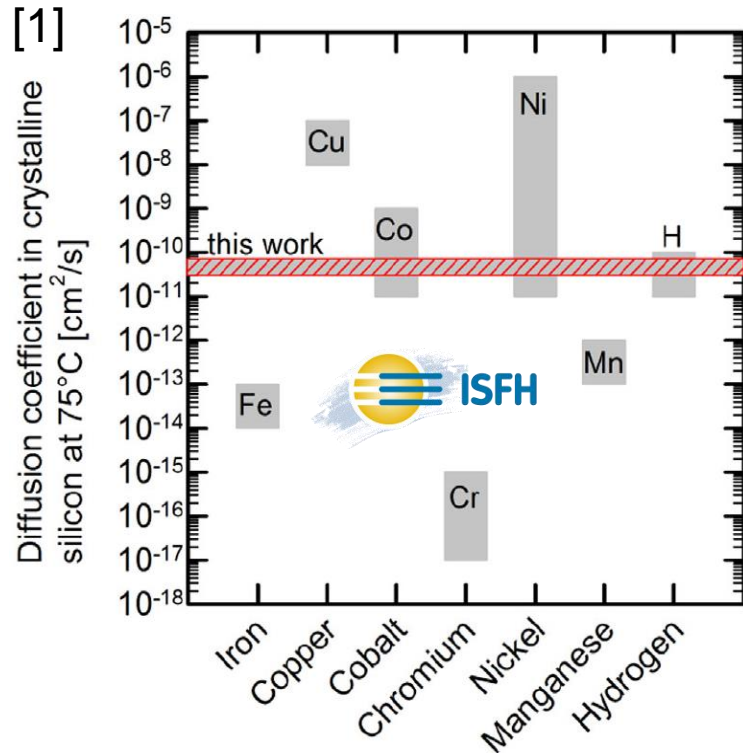
- In 2016, Bredemeier *et al.* proposed that metallic impurities (M) are the root cause of LeTID.



- Before firing:** metallic impurities reside in a recombination inactive precipitated state (M_p).
- Firing ($T > 600\text{ }^\circ\text{C}$):** precipitates dissolve into interstitials (M_i).
- Cooldown:** M_i bond with a homogeneously distributed impurity to form a M_i-X complex.
- Illuminated annealing:** The complex reconfigures itself into a M_i-X^* complex then dissociates into M_i

The Past – Evaluating the Root Cause – Metal Impurities

- In 2017, Bredemeier et al. suggested Co and Ni as a possible metal impurity
- It was suggested that diffusion of the metals towards the surface could explain regeneration.



- Deniz *et al.* (2018), found Ni precipitation using TEM and energy dispersive x-ray (EDX) measurements.
- TIDLS by UNSW, MIT – defect recombination properties (k -value) close to Ti_i^{+/++}, Mo_i^{0/+} or W_s^{0/+}.

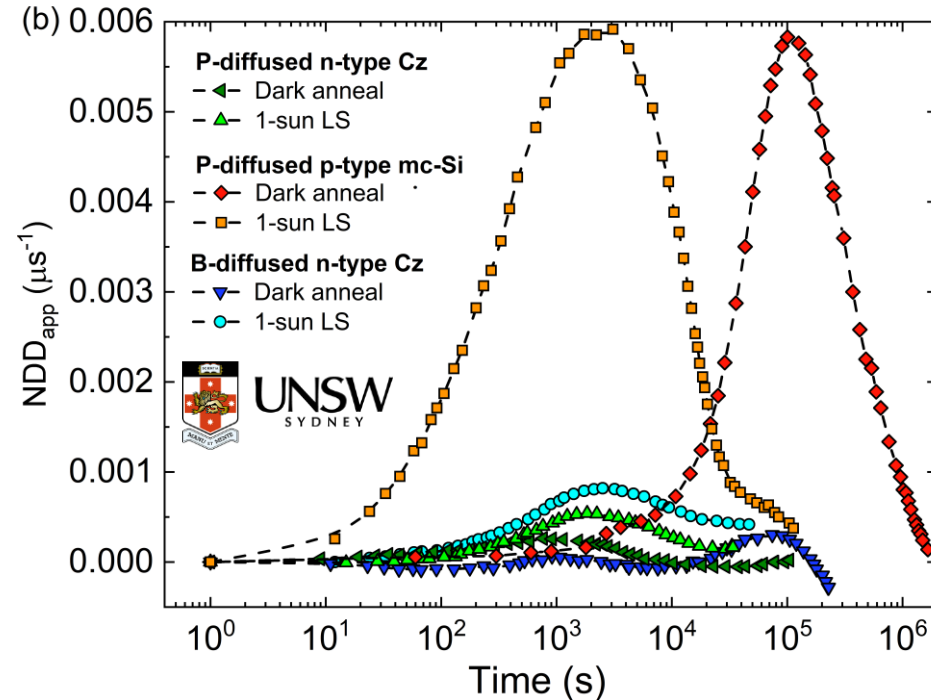
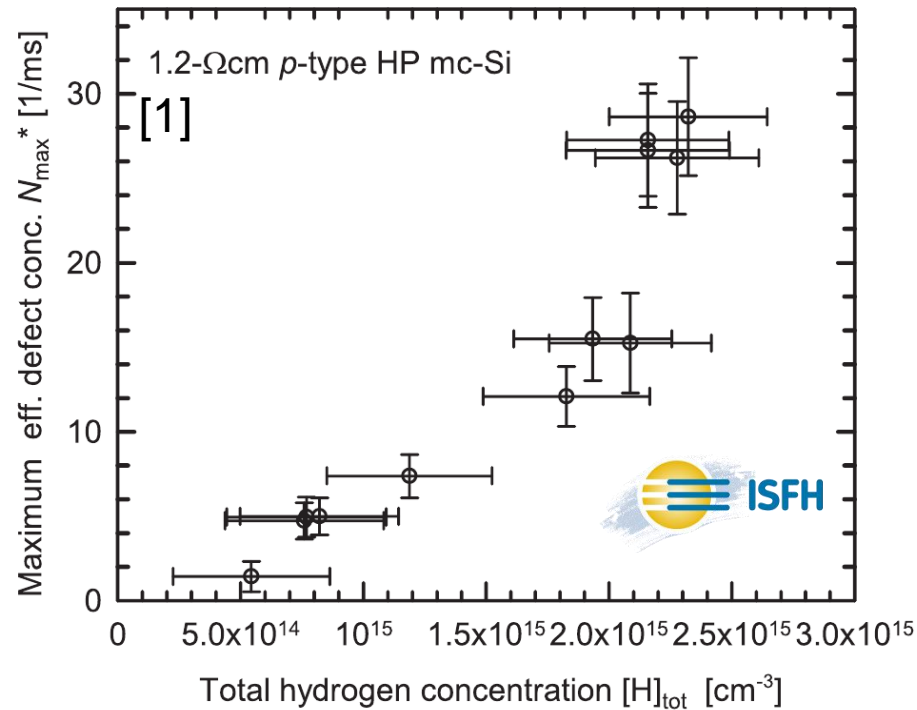
[1] Bredemeier *et al.*, Sol. RRL. 2 (2018) 1700159.

[2] Deniz *et al.*, Sol. RRL. 2 (2018) 1800170.

[3] Jensen *et al.*, 44th IEEE PVSC, 2017: pp. 3300–3303.

The Present – Hydrogen-Induced Degradation

- There are now many studies suggesting that hydrogen is responsible for LeTID.



- Recently, Schmidt *et al.* demonstrated for the first time, a direct correlation between $[H]$ and LeTID
- In experiments, we observe different amounts of LeTID in different materials.
 - Is something inherent to the wafer also involved – Could it be a H-X complex?

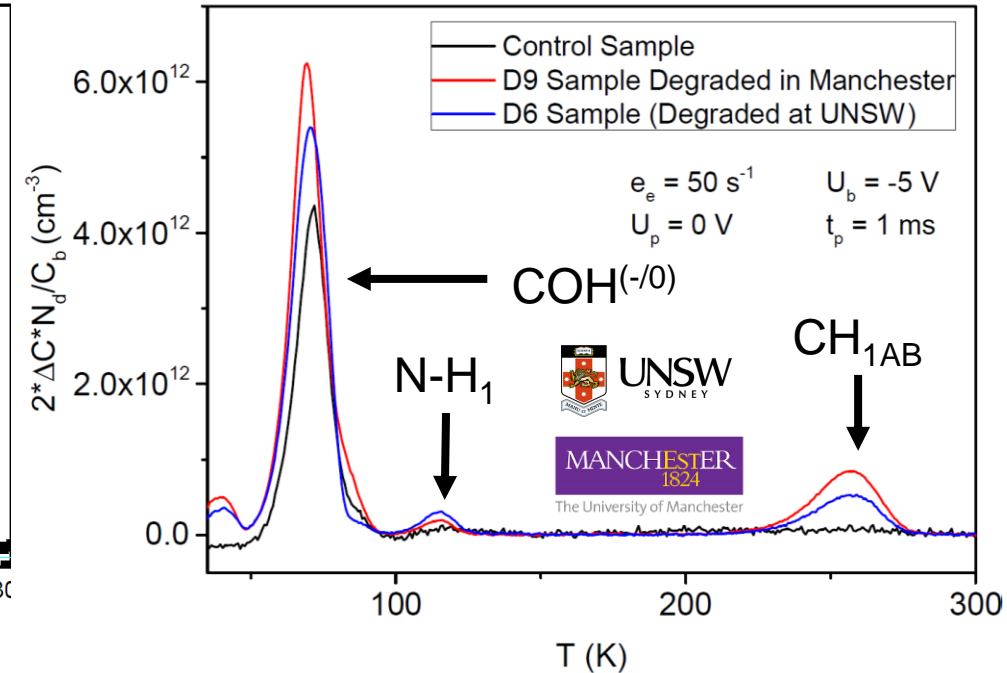
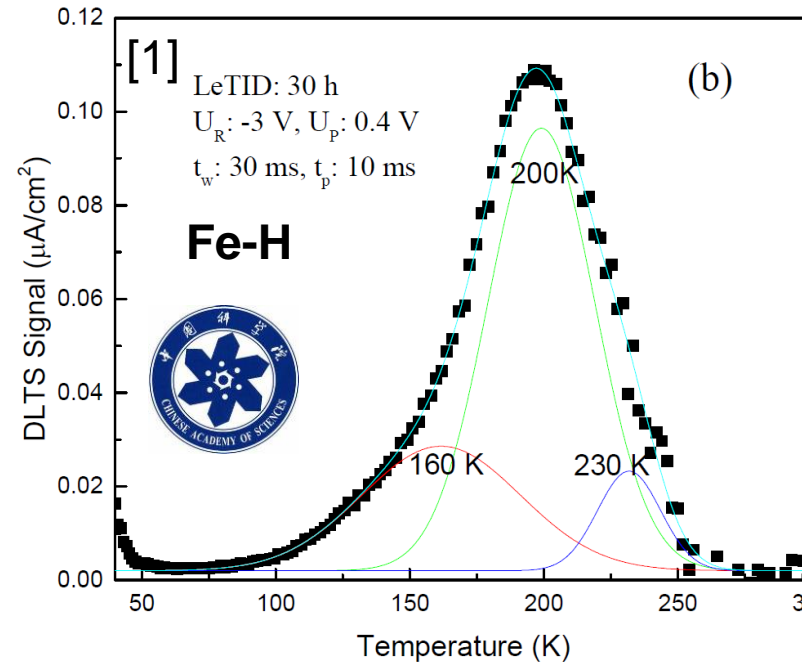
[1] Schmidt *et al.*, IEEE J. Photovoltaics. 9 (2019) 1497–1503.

The Present – H-X Complexes and Deep Level Transient Spectroscopy

- Hydrogen can form complexes with almost everything

- Ag-H_x (Graff 2000...)
- Au-H (Deixier 1998...)
- B-H (Sah 1983...)
- C-H (Anderson 2002...)
- C-O-H (Vaquero-Contreras 2017)
- Co-H_x (Scheffler 2013...)
- Cr-H (Sadoh 1994...)
- Cu-H (Yarykin 2013...)
- Fe-H (Szwacki 2007...)
- Ni-H_x (Shiraishi 1999...)
- P-H (Seager 1990...)
- Pd-H (Jones 1999...)
- Pt-H_x (Hohne 1994...)
- Si-V-H_x & Si-V-O-H_x (Bonde 1999)
- Ti-H_x (Scheffler 2015...)
- V_x-H_y (Graff 2000...)
- Va-H_x (Sadoh 1992...)
- And many more.....

- DLTS is a good method for identifying recombination active traps

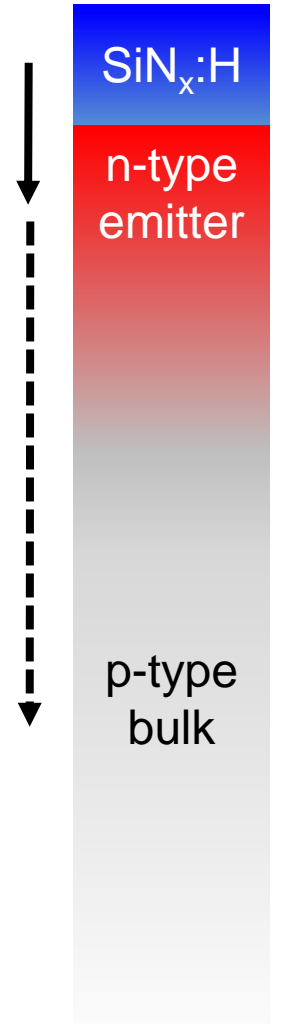
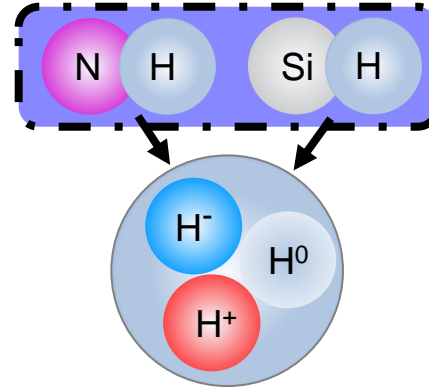
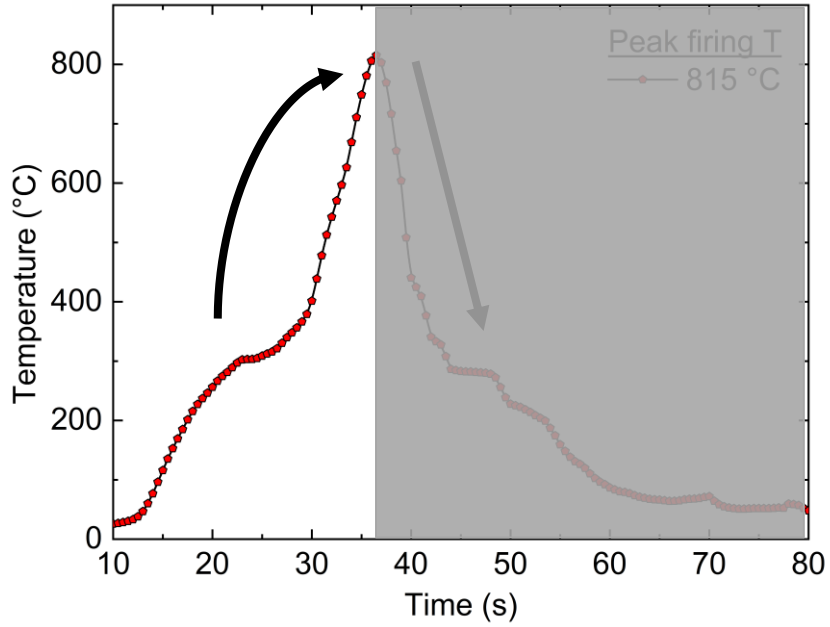


- Recent DLTS studies have hypothesised that **Fe-H** or **C-H** complexes may be defect behind LeTID. Further measurements are needed to confirm this.

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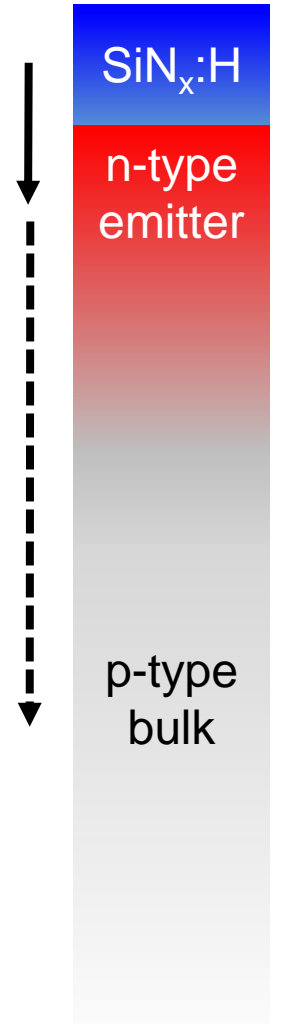
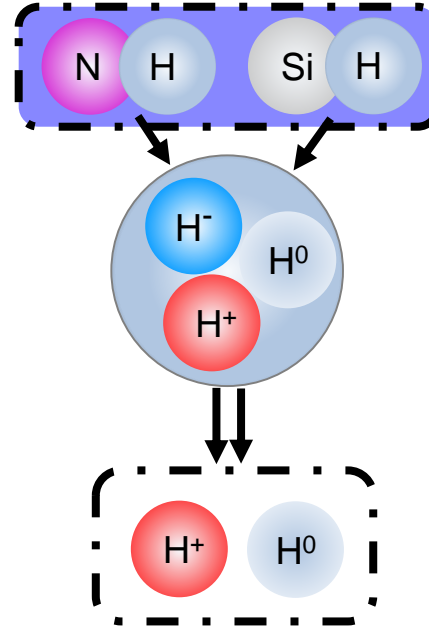
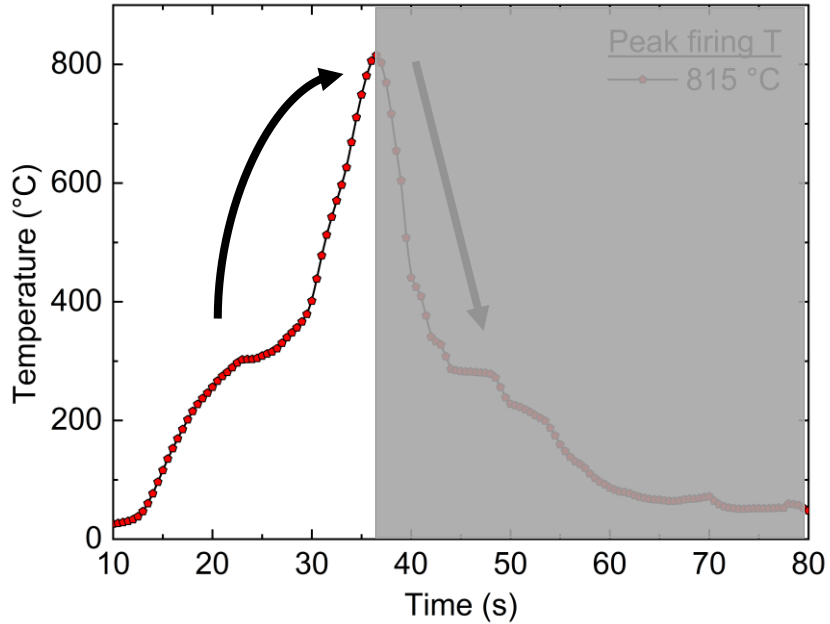
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The Present – A Hydrogen-X Defect Model



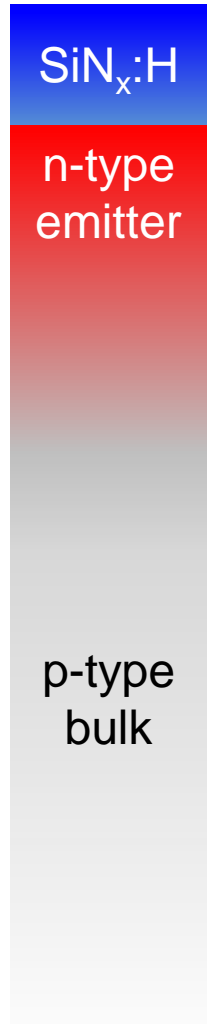
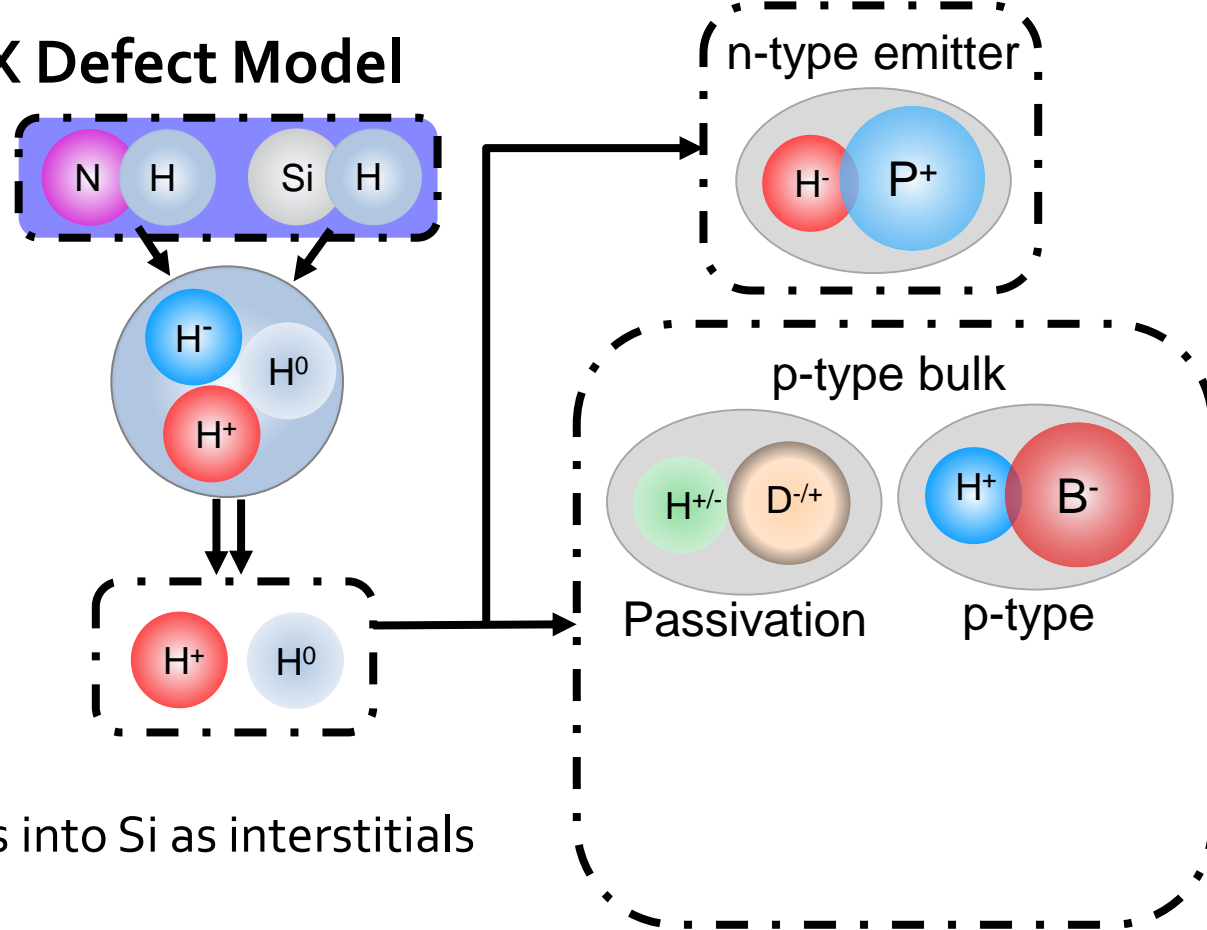
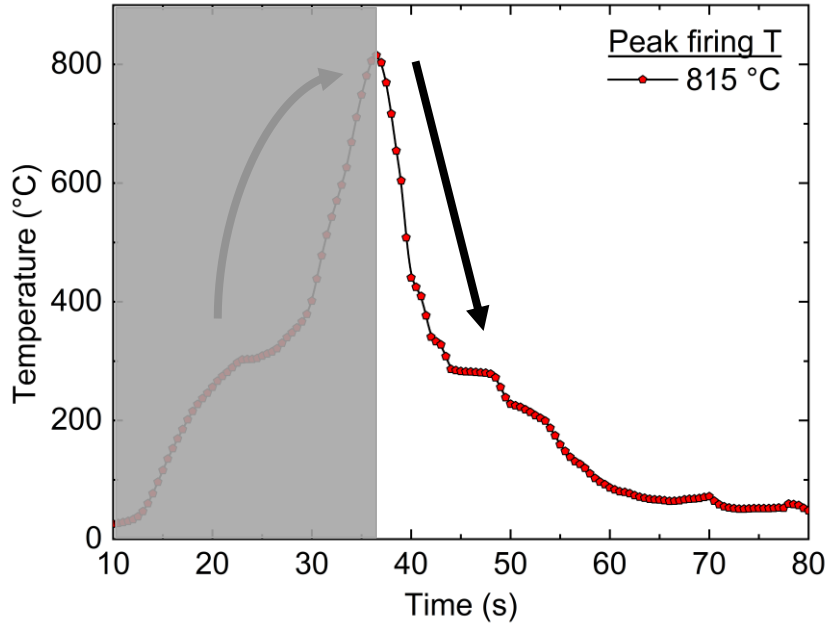
- During firing (peak) – H diffuses into Si as interstitials

The Present – A Hydrogen-X Defect Model



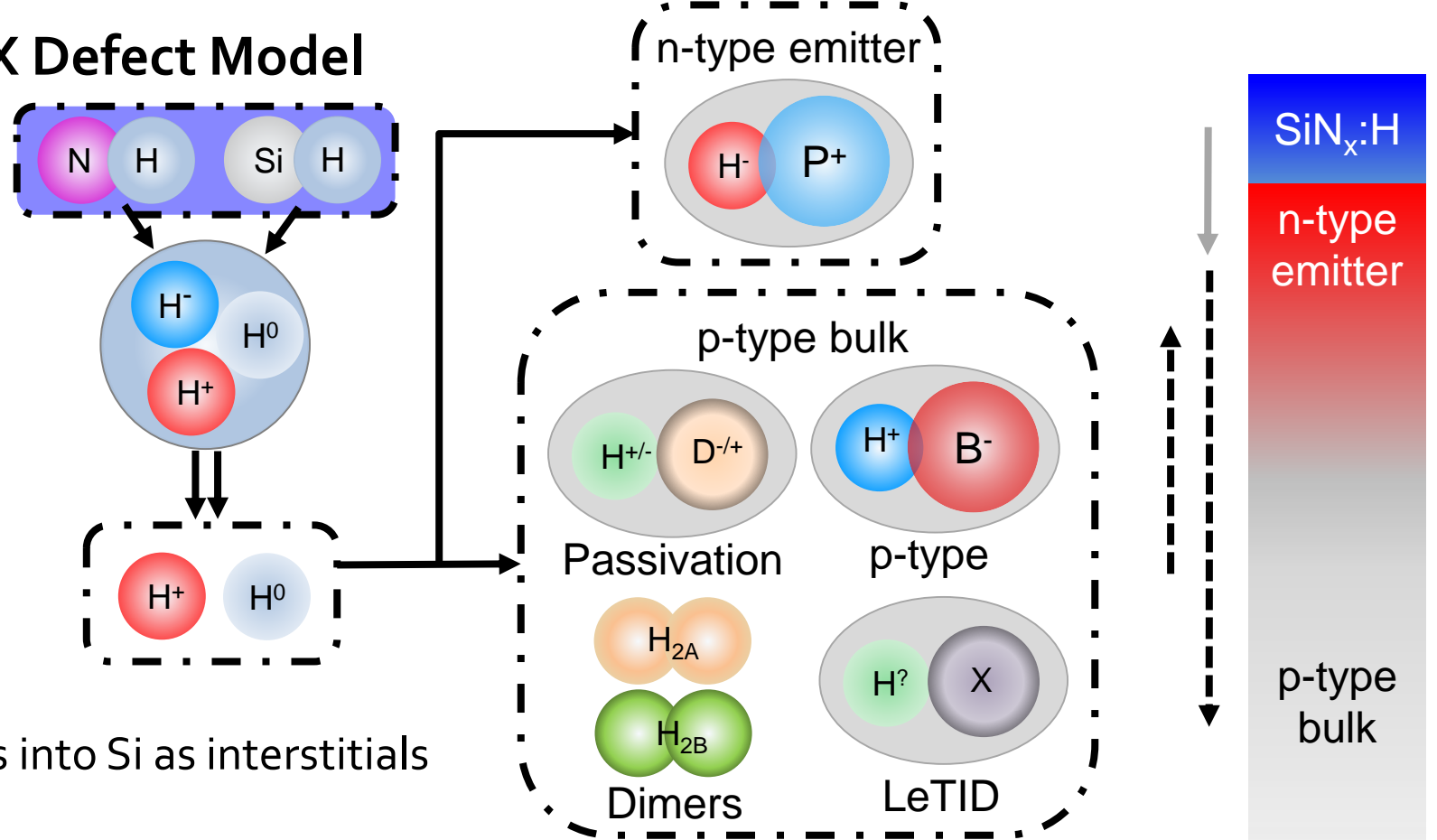
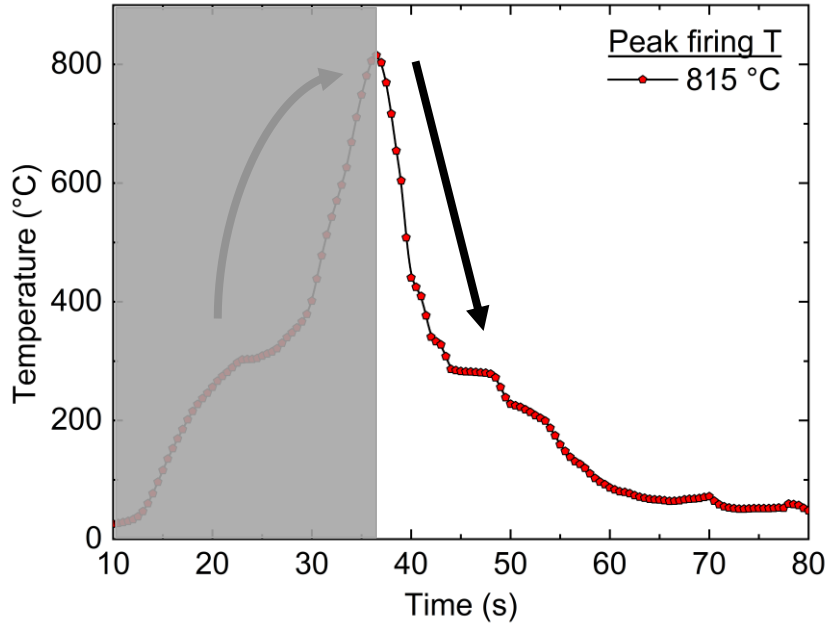
- **During firing (peak)** – H diffuses into Si as interstitials
- At high temperatures, the Si conductivity is intrinsic \rightarrow H is largely in the H^+ state

The Present – A Hydrogen-X Defect Model



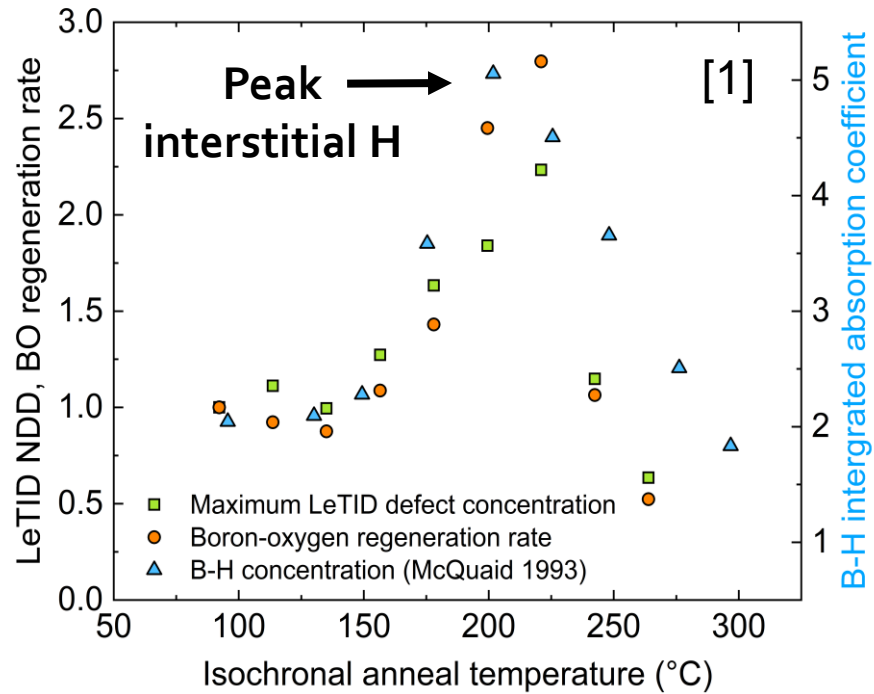
- **During firing (peak)** – H diffuses into Si as interstitials
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- **During cooling (quenching)** – H forms B-H pairs in the bulk and passivates defects.

The Present – A Hydrogen-X Defect Model

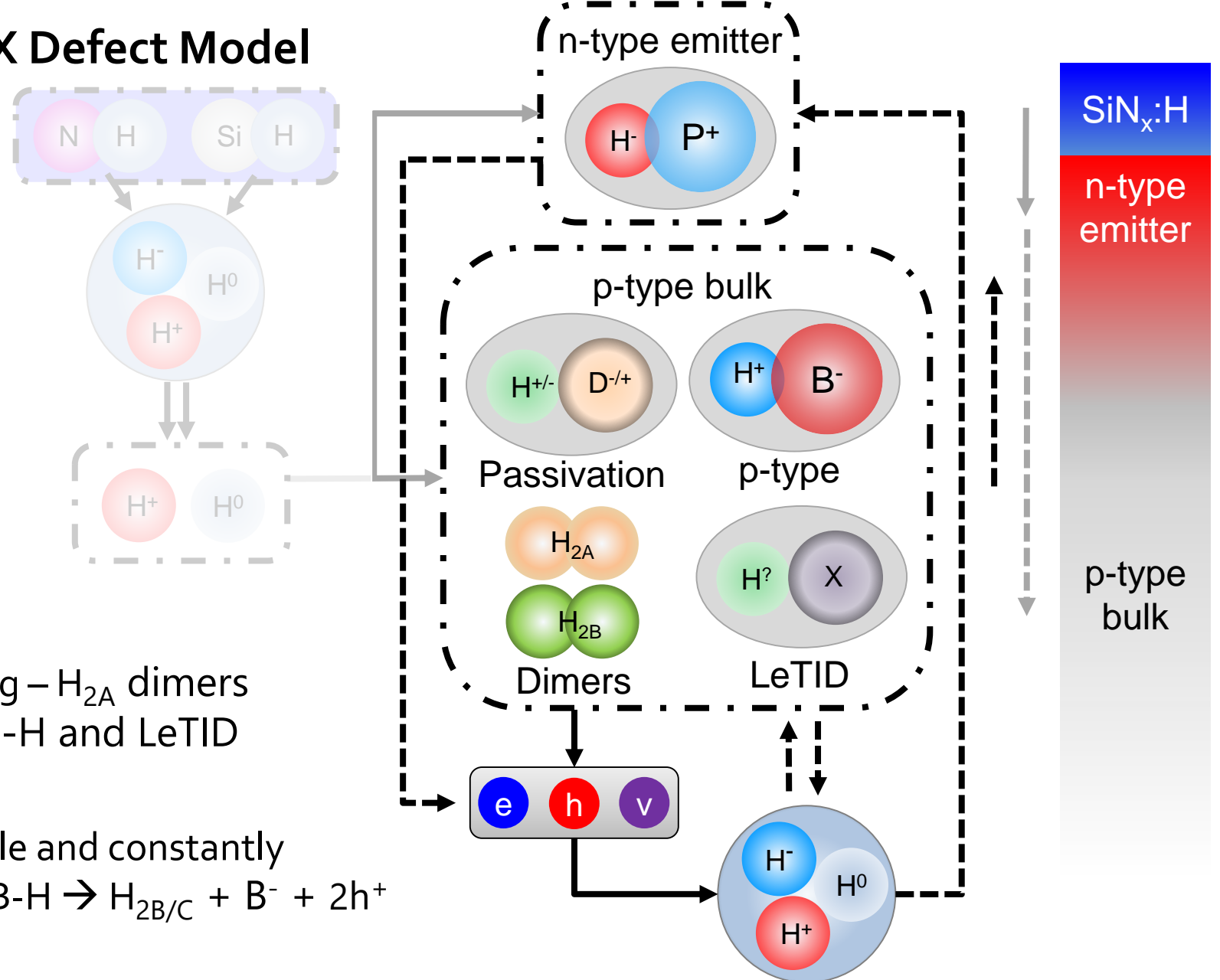


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- At high temperatures, the Si conductivity is intrinsic → H is largely in the H⁺ state
- **During cooling (quenching)** – H forms B-H pairs in the bulk and passivates defects.
- It also pre-forms LeTID, however, a majority of H is frozen in metastable dimer states (H_{2A/B})

The Present – A Hydrogen-X Defect Model

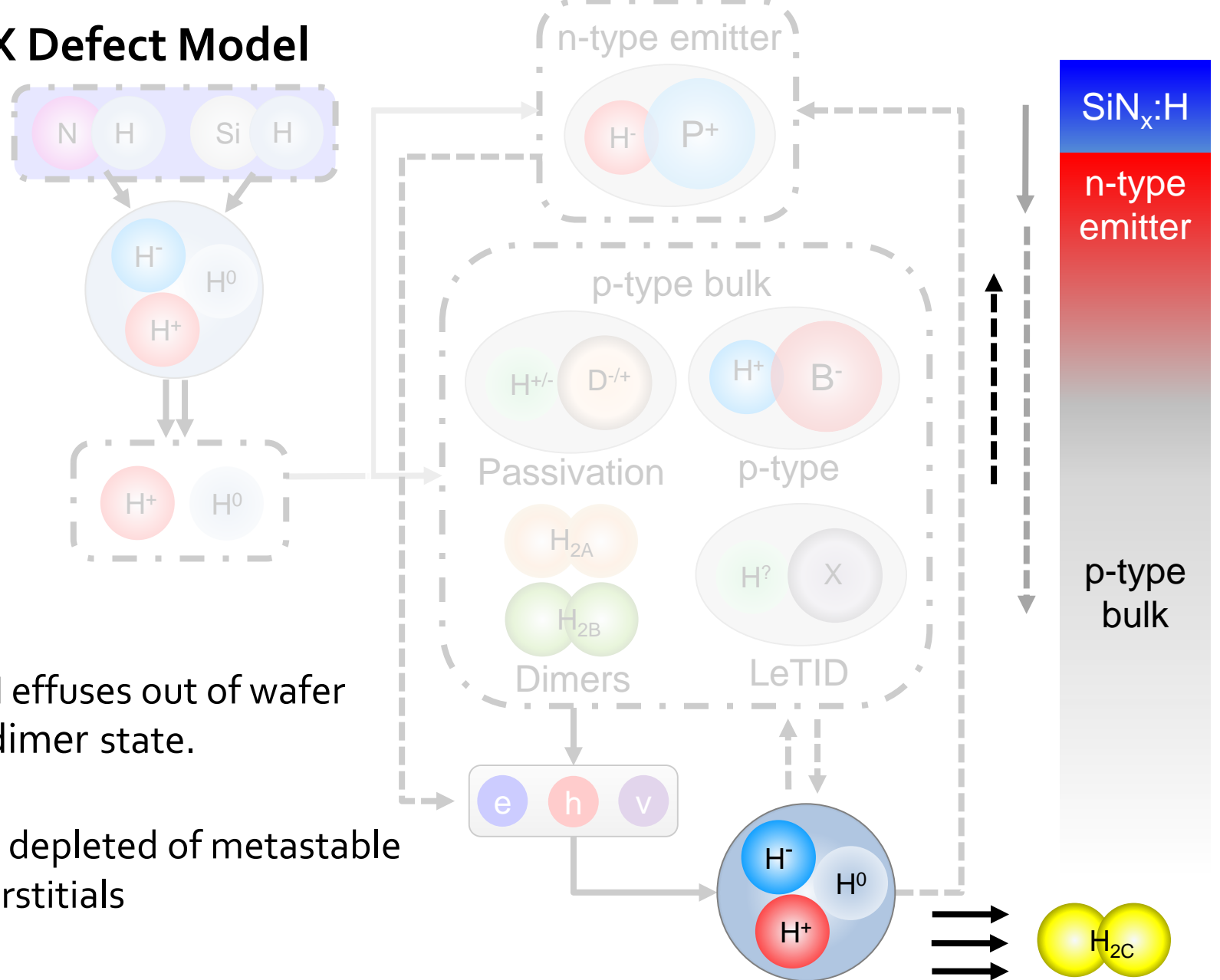
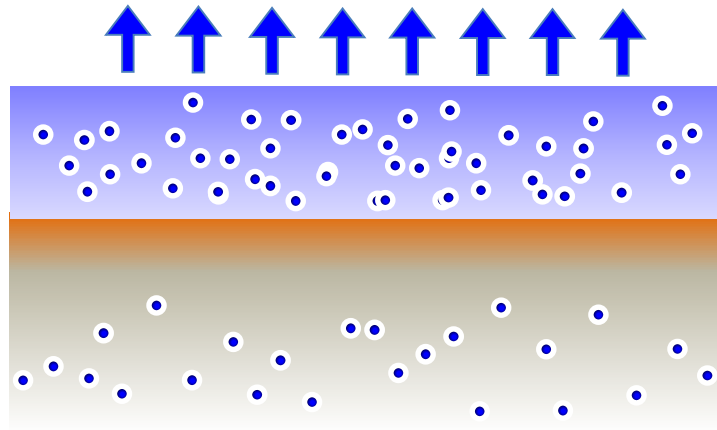


- During annealing or light soaking – H_{2A} dimers dissociate and contribute to B-H and LeTID
- All of these bonds are metastable and constantly breaking and forming e.g. $H^+ + B-H \rightarrow H_{2B/C} + B^- + 2h^+$



[1] Fung *et al.*, AIP Conf. Proc., 2018: p. 130004.

The Present – A Hydrogen-X Defect Model



- Net motion of H is towards the surface and out of silicon.
- With long-duration annealing, H effuses out of wafer or transforms into a stable H_{2C} dimer state.
- LeTID recovers when the bulk is depleted of metastable dimers, bound states and H interstitials

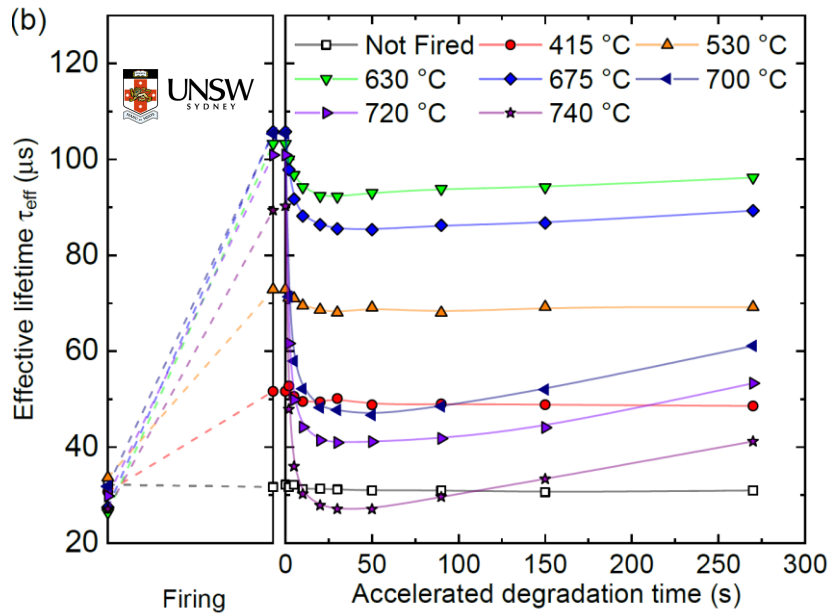
[1] Fung *et al.*, AIP Conf. Proc., 2018: p. 130004.

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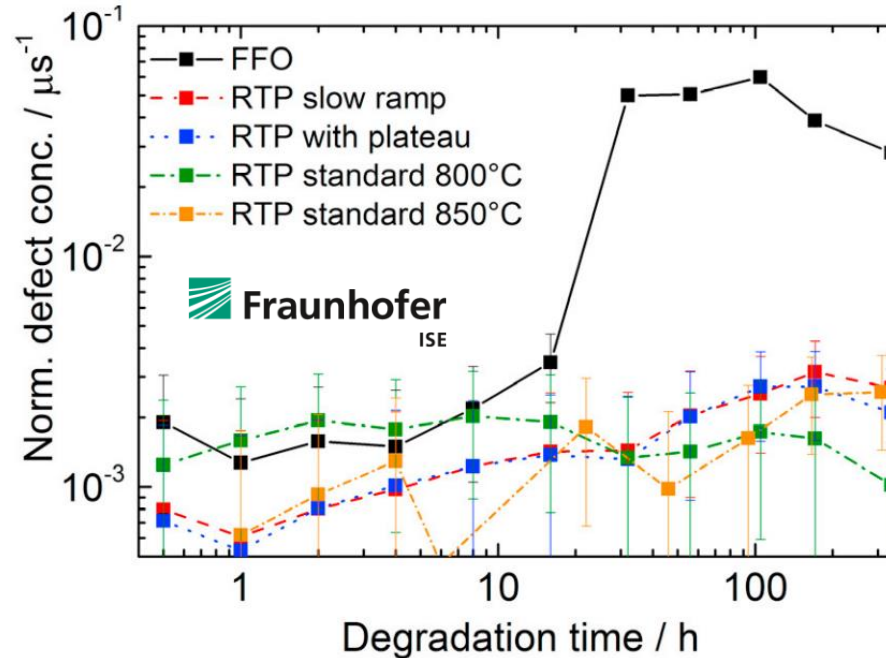
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The Present – Mitigation of LeTID – Process Modification

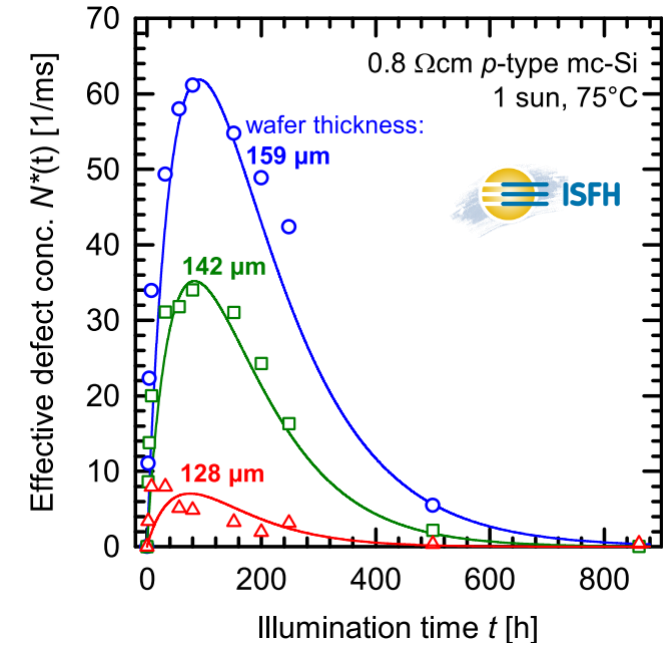
- There are many ways of reducing the hydrogen content within the silicon wafers to reduce LeTID



Chan *et al.*, IEEE J. Photovoltaics. 6 (2016) 1473–1479.



R. Eberle *et al.*, Energy Procedia, (2017) pp. 712–717.

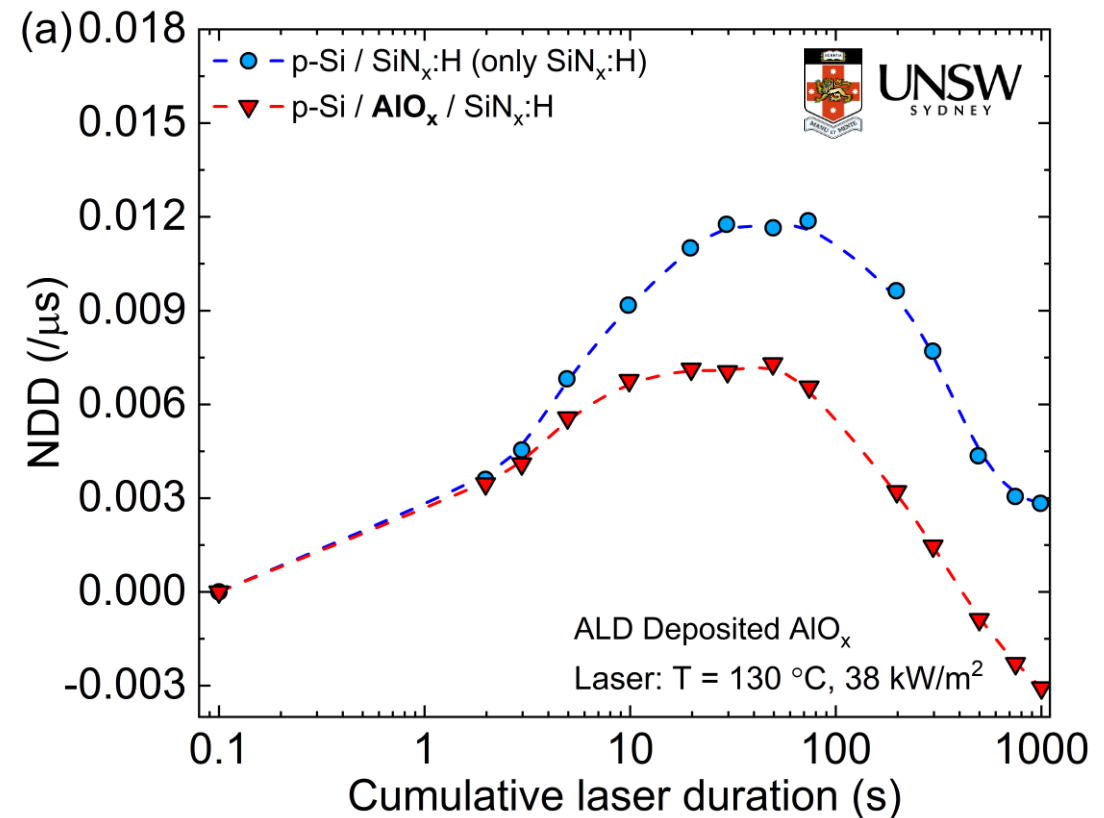
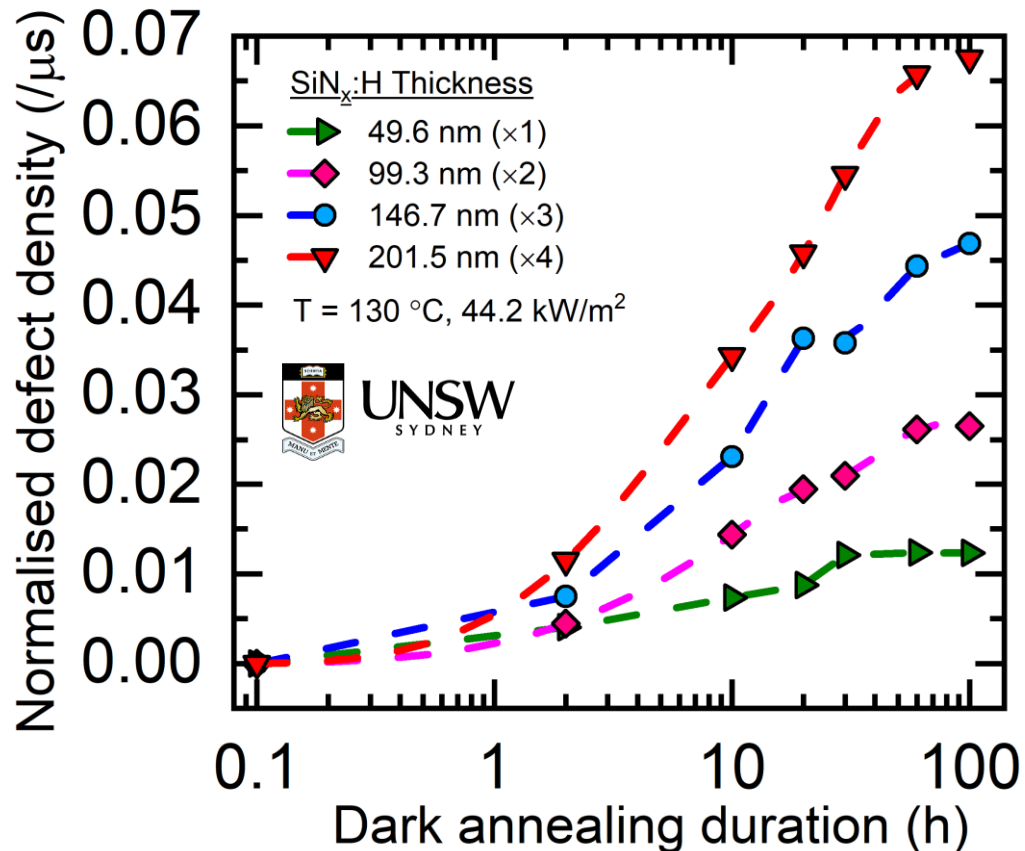


Schmidt *et al.*, IEEE J. Photovoltaics. 9 (2019) 1497–1503

- Reducing peak firing \rightarrow Less H in-diffusion or Slower-cooling \rightarrow More H effusion
- Thinner wafers have demonstrated lower LeTID \rightarrow Faster defect effusion

The Present – Mitigation of LeTID – Process Modification

- We can also reduce the hydrogen content within the $\text{SiN}_x\text{:H}$ films.
- Reducing the thickness of $\text{SiN}_x\text{:H}$ \rightarrow lower Si-H and N-H bond density \rightarrow lower [H] released during firing
- Deposition of **ALD** AlO_x under the $\text{SiN}_x\text{:H}$ as barrier for hydrogen in-diffusion

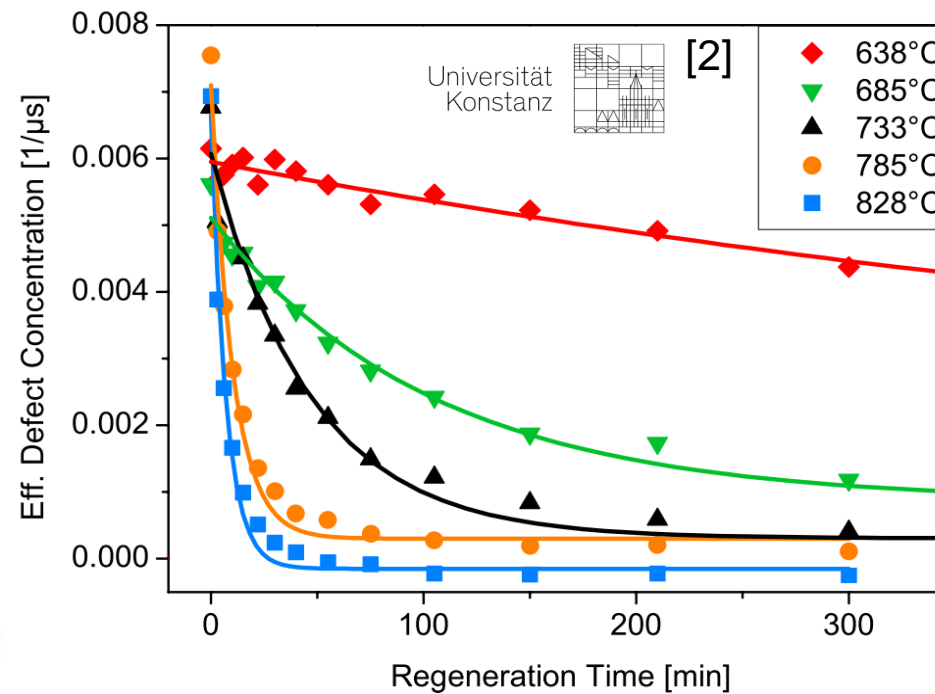
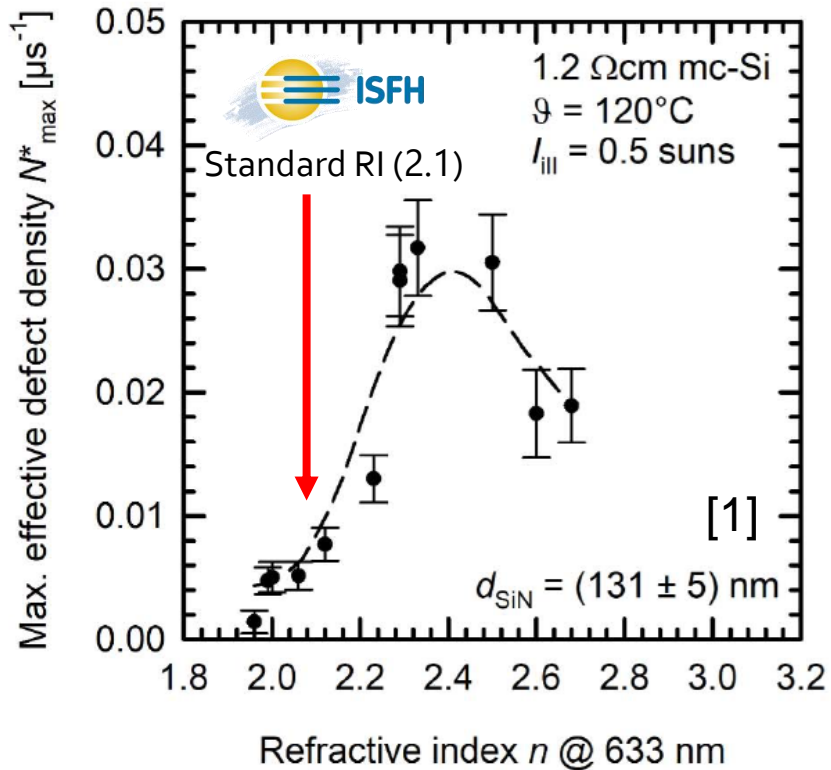


[1] Varshney *et al.*, IEEE J. Photovoltaics. 9 (2019) 601–607.

[2] Varshney *et al.*, IEEE J. Photovoltaics, 2019 (in press)

The Present – Mitigation of LeTID – Process Modification

- Tuning the SiN_x:H refractive index to release less hydrogen during firing
- At low RI < 1.9, SiN_x:H films have high atomic density → reduces H diffusivity
- Hydrogen is important as it allows for the passivation of bulk defects (e.g. B-O in p-type)
- Lower [H] causes B-O regeneration to become slower → LID mitigation techniques become less effective.



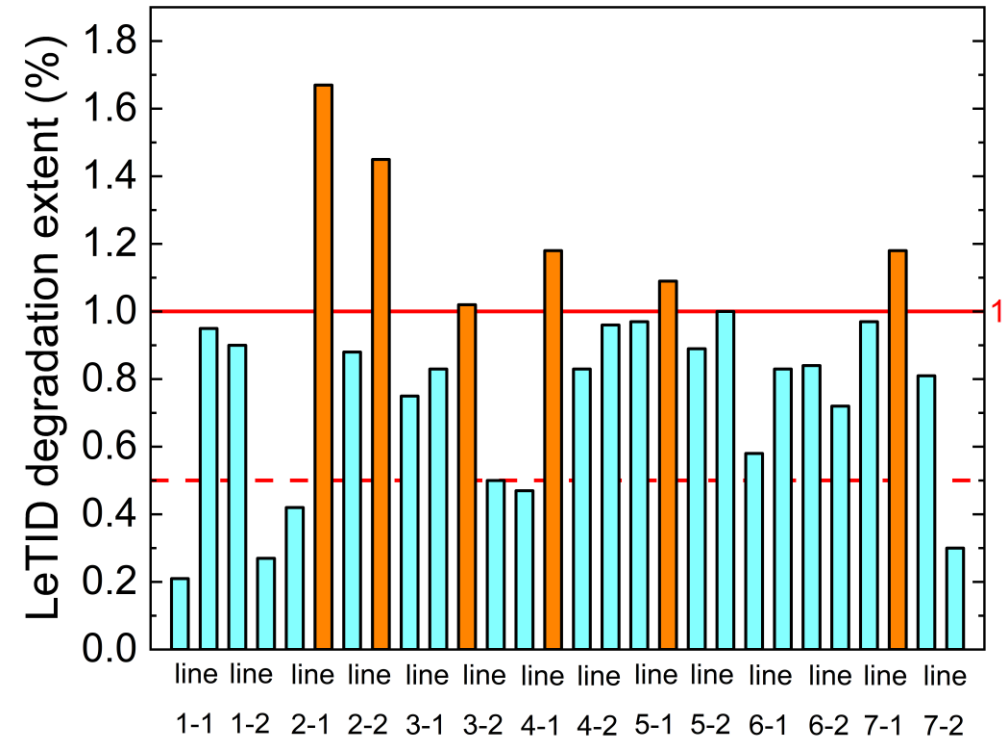
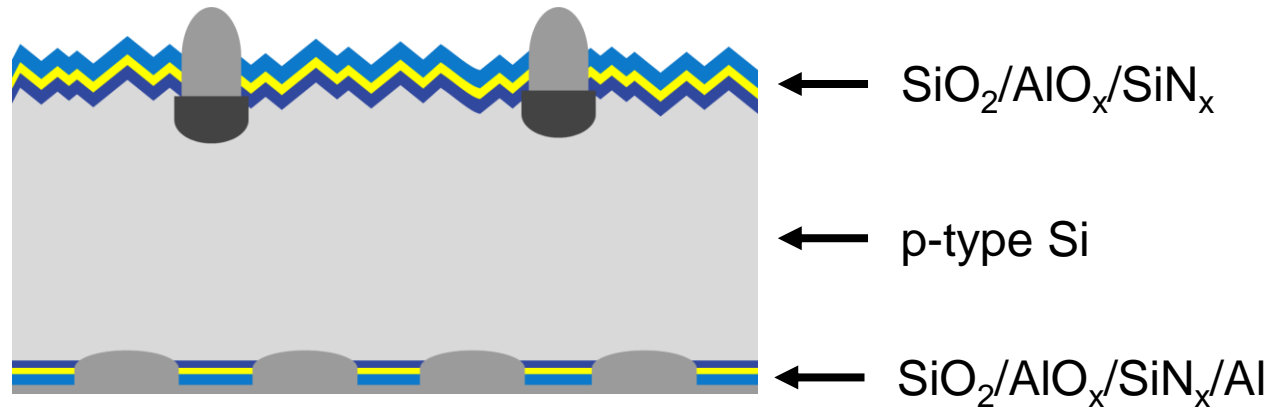
- Commercial LeTID mitigation usually involves post-cell treatments

1. Light based treatments
2. Current Injection
3. Biased annealing

[1] Bredemeier *et al.*, Phys. Status Solidi – Rapid Res. Lett. 13 (2019) 1900201.

[2] Wilking *et al.*, J. Appl. Phys. 114 (2013) 194512

The Present – An Example of Commercial ANTI-LeTID Solar Cells and Modules

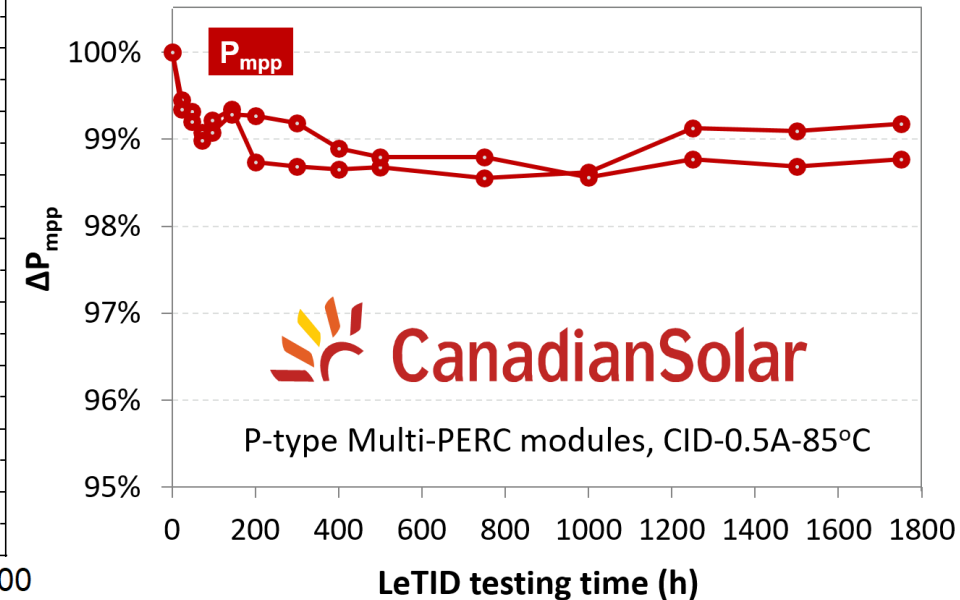
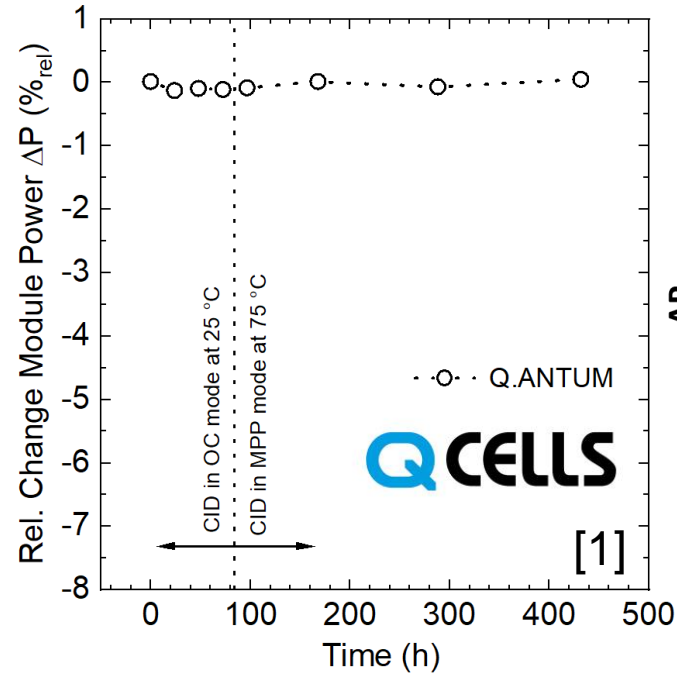
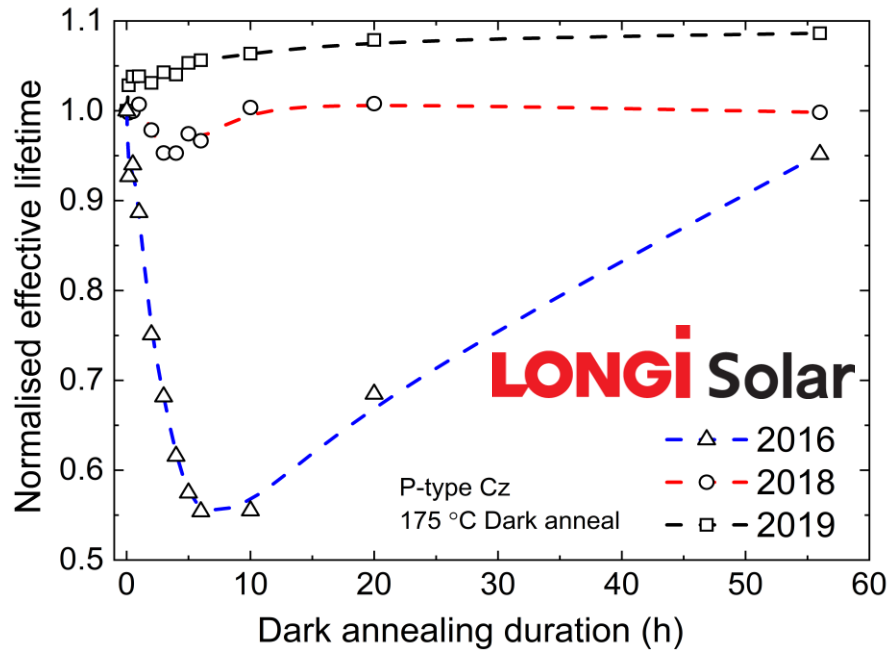


- Risen solar (Jäger Series) combine many techniques
1. Low temperature firing – reduces hydrogen in-diffusion
 2. Current-injection post-cell processing
 3. ALD $\text{AlO}_x:\text{H}$ passivation on both sides – hydrogen lean blocking layer
 4. SiO_2 layer on both sides – hydrogen blocking layer



What Lies Ahead – Will LeTID Remain a Problem for Commercial PV?

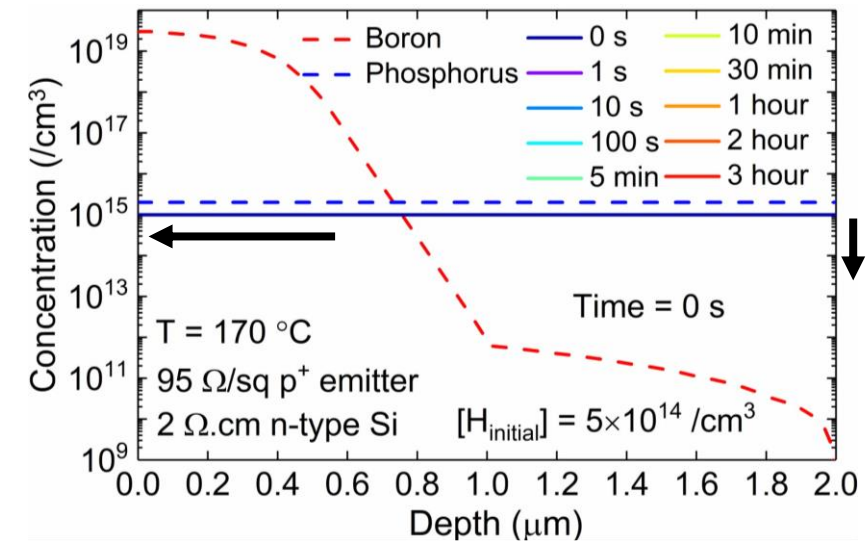
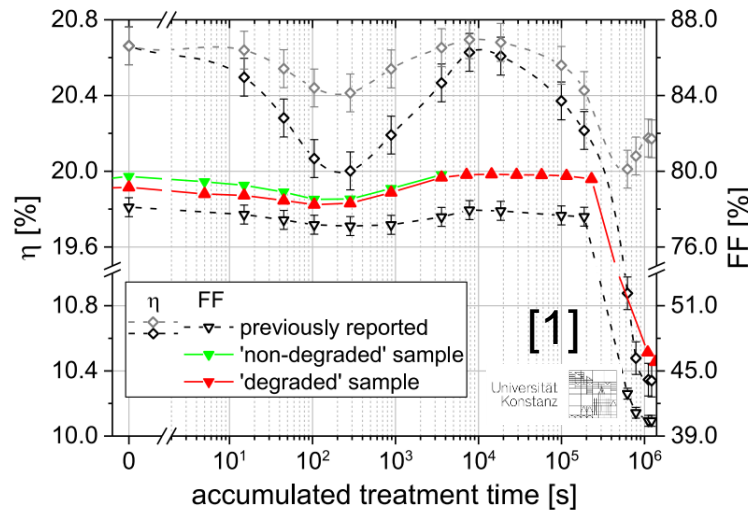
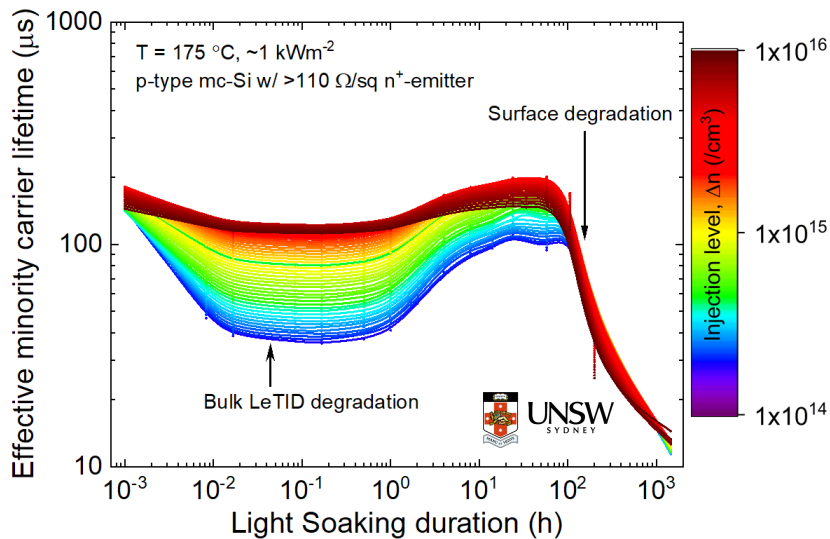
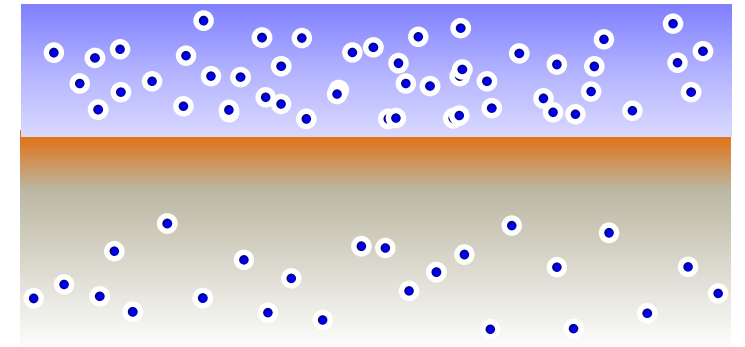
LeTID is both a material-inherent and process-induced defect



- Wafer quality is constantly improving with some wafers that are already LeTID free.
- Choosing better wafer sources + applying mitigation treatments will solve LeTID in both mc-Si and Cz-Si

What Lies Ahead – Hydrogen-Induced Surface Degradation

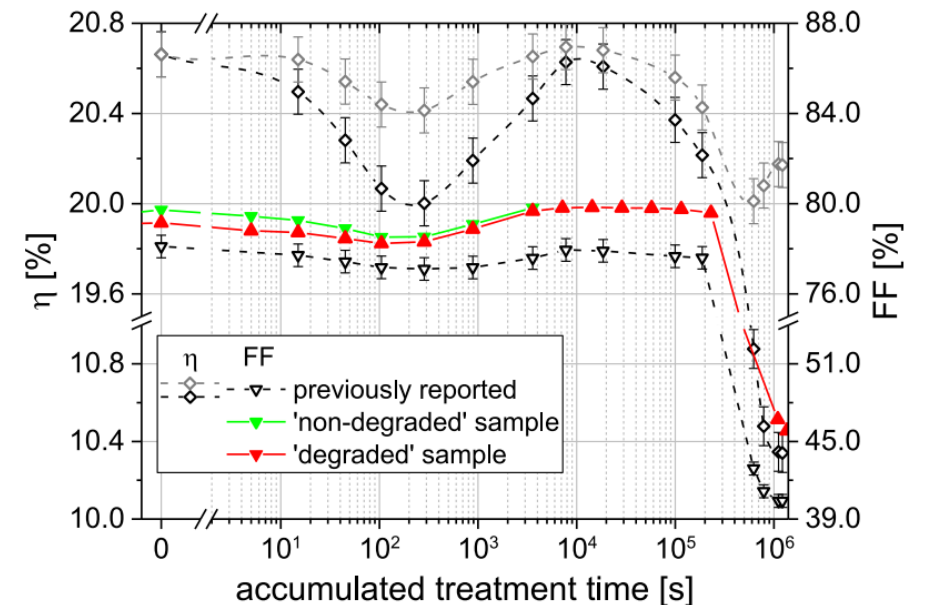
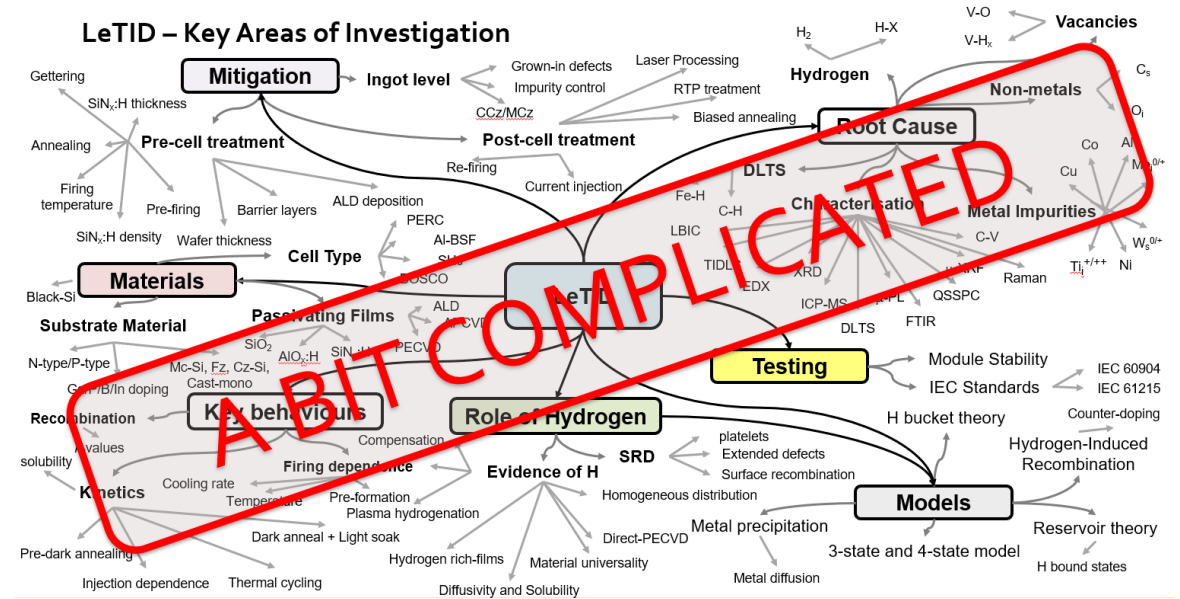
- As LeTID recovers, hydrogen diffuses out towards the surfaces.
- Too much H at the interface can lead to the formation of hydrogen-induced defects → surface degradation (increased J_{0s}).
- On PERC cells, this long-term degradation can cause up to a **10% absolute** drop in efficiency due to an decrease in FF [1].



[1] Herguth *et al.*, IEEE J. Photovoltaics. (2018) 1–12.

Summary

- LeTID is a complicated but well understood problem.
- There are many mitigation techniques for commercial PERC solar cell
- Beyond LeTID, we need to start assessing the impact of hydrogen-induced surface degradation and finding solutions.
- I hope that you have learnt something from my talk!





Thank you for your attention. Daniel.chen@unsw.edu.au